

Dielectric Solids / Insulators

Macroscopic description

dielectric polarisation $\mathbf{P} = \chi_e \epsilon_0 \mathcal{E}$

$$8.854187817 \times 10^{-12} \text{ C}^2 \text{J}^{-1} \text{m}^{-1}$$

dielectric susceptibility χ_e (> 0)

dielectric constant $\epsilon = \chi_e + 1$

microscopic dipole $\mathbf{p} = q\delta$

$$\mathbf{P} = \frac{N}{V} \mathbf{p} = \frac{N}{V} q\delta$$

Plane-plate capacitor

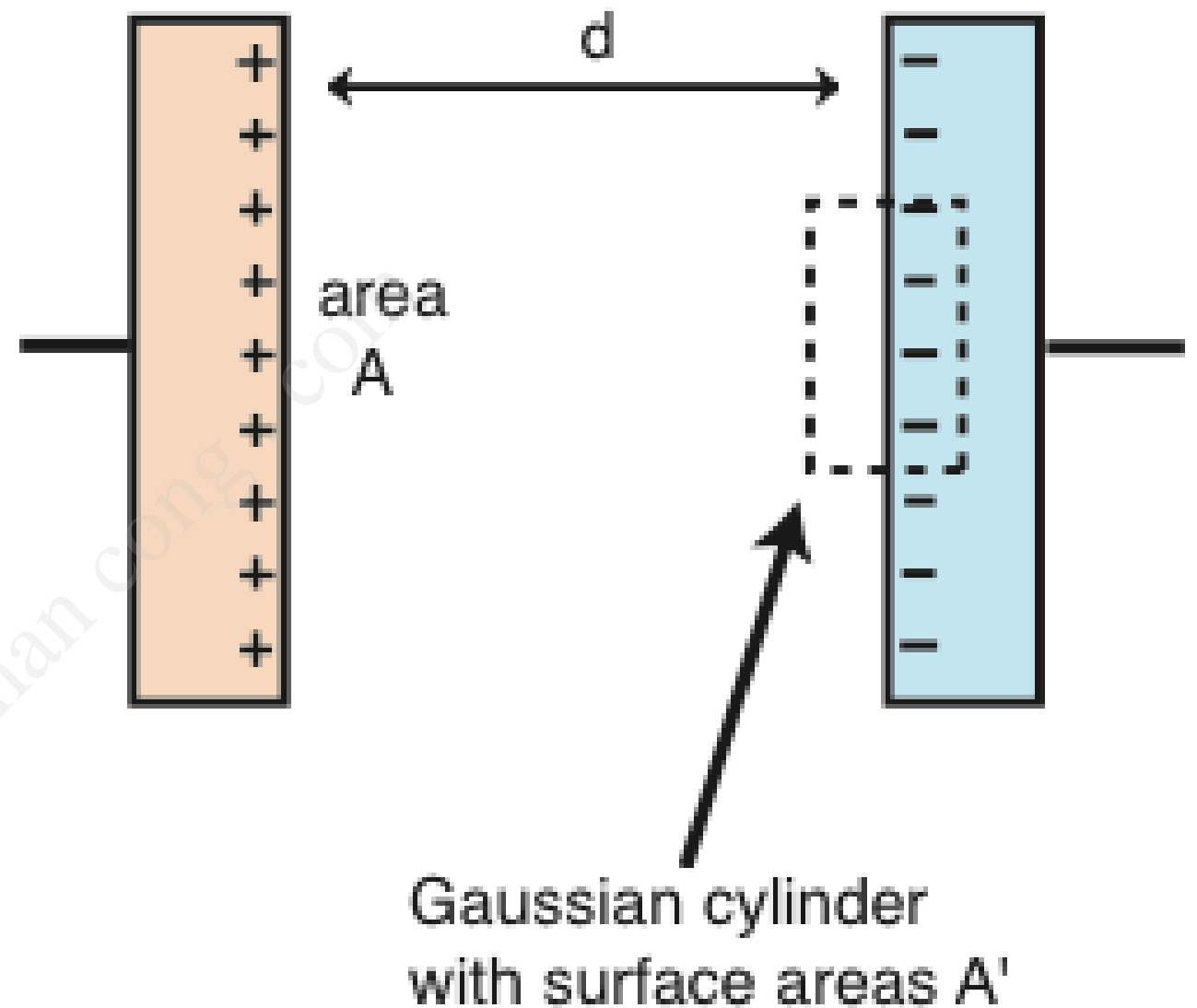
$$\oint \mathbf{E} d\mathbf{A} = \oint \mathbf{E}_{\perp} dA = \frac{Q_{encl}}{\epsilon_0}$$

$$\mathbf{E} A' = \frac{\sigma A'}{\epsilon_0}$$

$$\mathbf{E} = \frac{\sigma}{\epsilon_0}$$

$$C = Q \frac{1}{U} = \sigma A \frac{1}{\mathbf{E} d}$$

$$= \sigma A \frac{\epsilon_0}{\sigma d} = \frac{A \epsilon_0}{d}$$



- High capacitance can be achieved by large A or small d.
- Both approaches give rise to several problems.

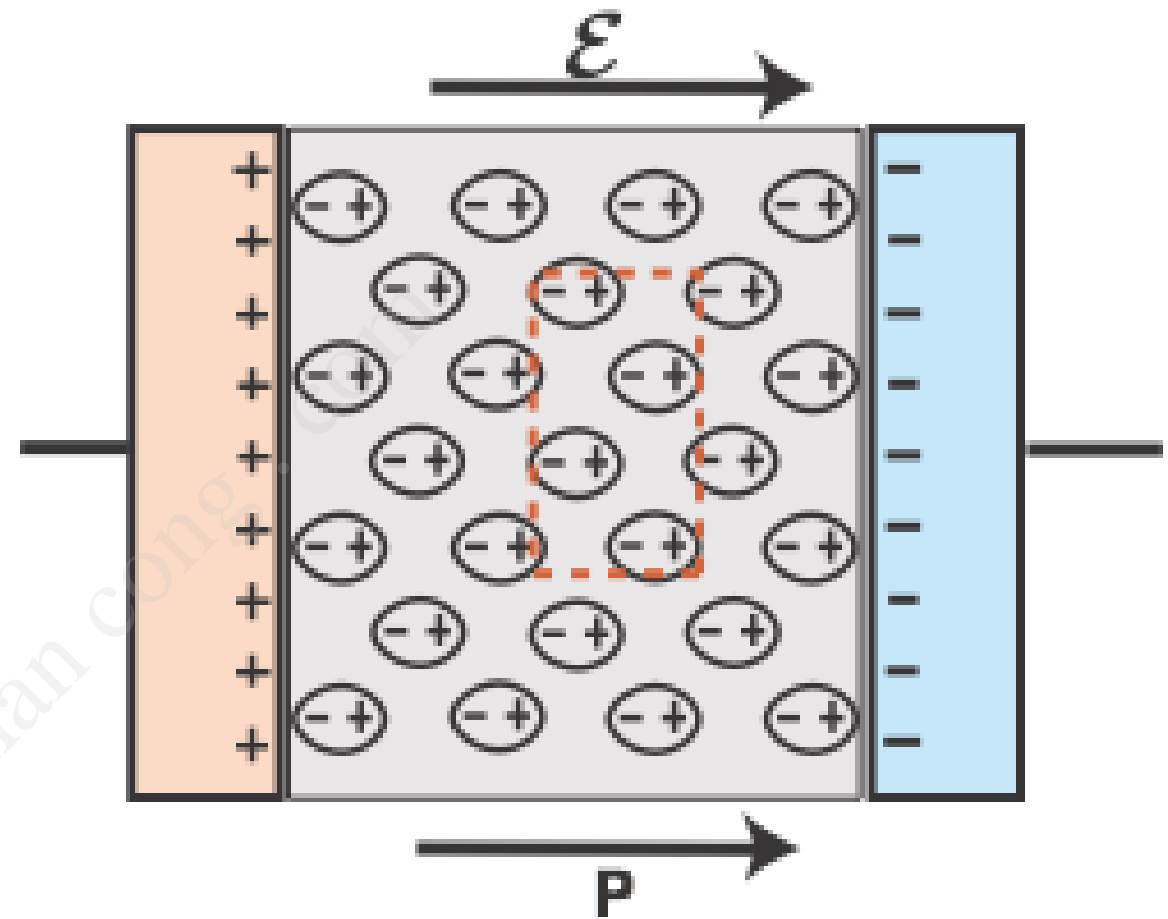
Plane-plate capacitor with dielectric

polarizable units:

$$p = q\delta$$

for the solid

$$P = \frac{N}{V} q\delta$$



- For any macroscopic Gaussian surface inside the dielectric, the incoming and outgoing electric field is identical (because the total average charge is 0).
- The only place where something macroscopically relevant happens are the surfaces of the dielectric.

Plane-plate capacitor with dielectric

$$Q_P = A \frac{N}{V} q \delta$$

$$\sigma_P = \frac{N}{V} \delta q = P$$

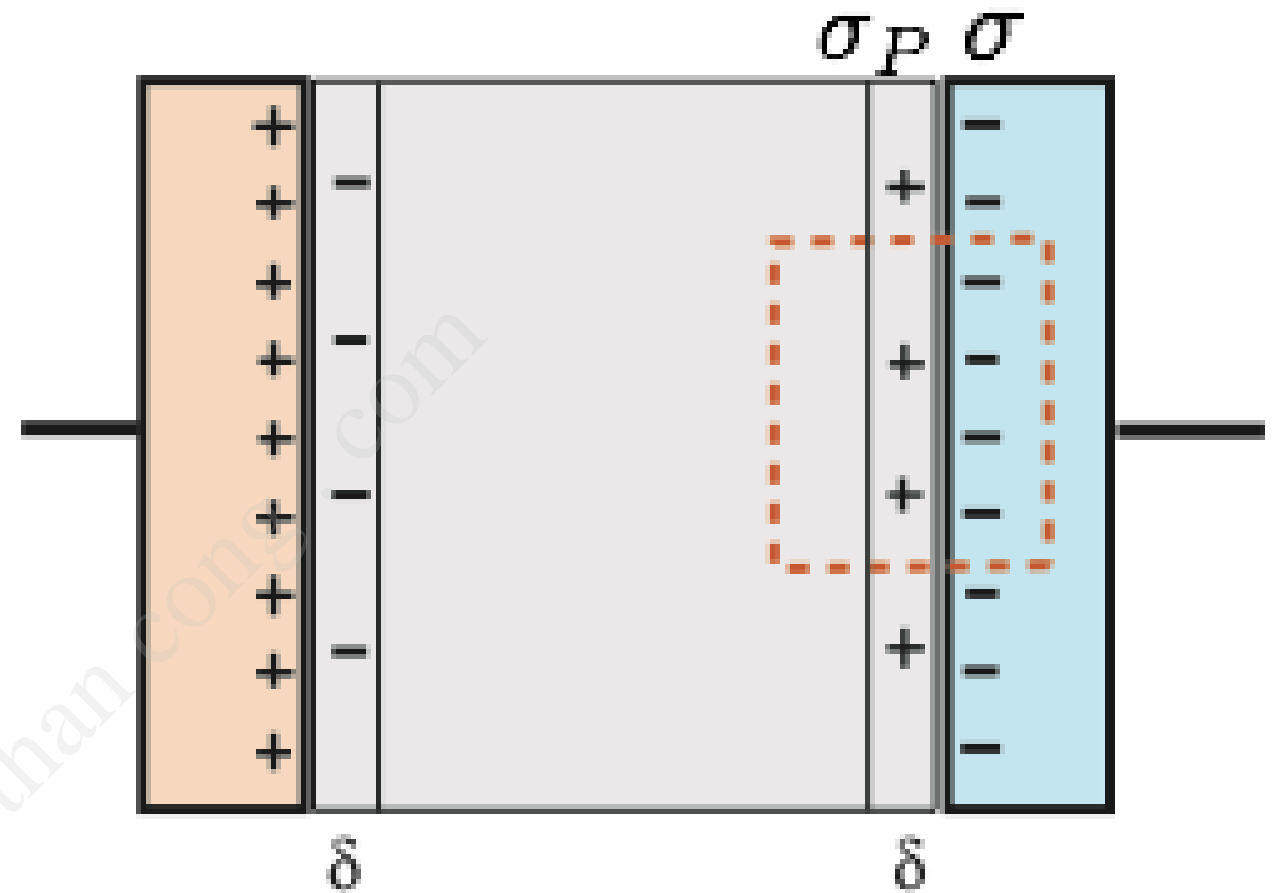
$$\mathcal{E} = \frac{\sigma - \sigma_P}{\epsilon_0} = \frac{1}{\epsilon_0} (\sigma - P)$$

$$P = \epsilon_0 \chi_e \mathcal{E}$$

$$\mathcal{E} = \frac{\sigma}{\epsilon_0 (1 + \chi_e)} = \frac{\sigma}{\epsilon_0 \epsilon}$$

$$\epsilon = 1 + \chi_e$$

so the E-field decreases
by a factor of ϵ



capacitance increase by a factor of ϵ

$$C = \frac{A \epsilon_0 (1 + \chi_e)}{d} = \frac{\epsilon \epsilon_0 A}{d}$$

The quest for materials with high Σ



gate area $A = l^2$

required charge to make it work $Q = CU = \frac{UA\epsilon\epsilon_0}{d}$

The dielectric constant

material	dielectric constant ϵ
vacuum	1
air	1.000576 (283 K, 1013 hPa)
rubber	2.5 - 3.5
SiO ₂	3.9
glass	5-10
NaCl	6.1
ethanol	25.8
water	81.1
strontium titanate	350

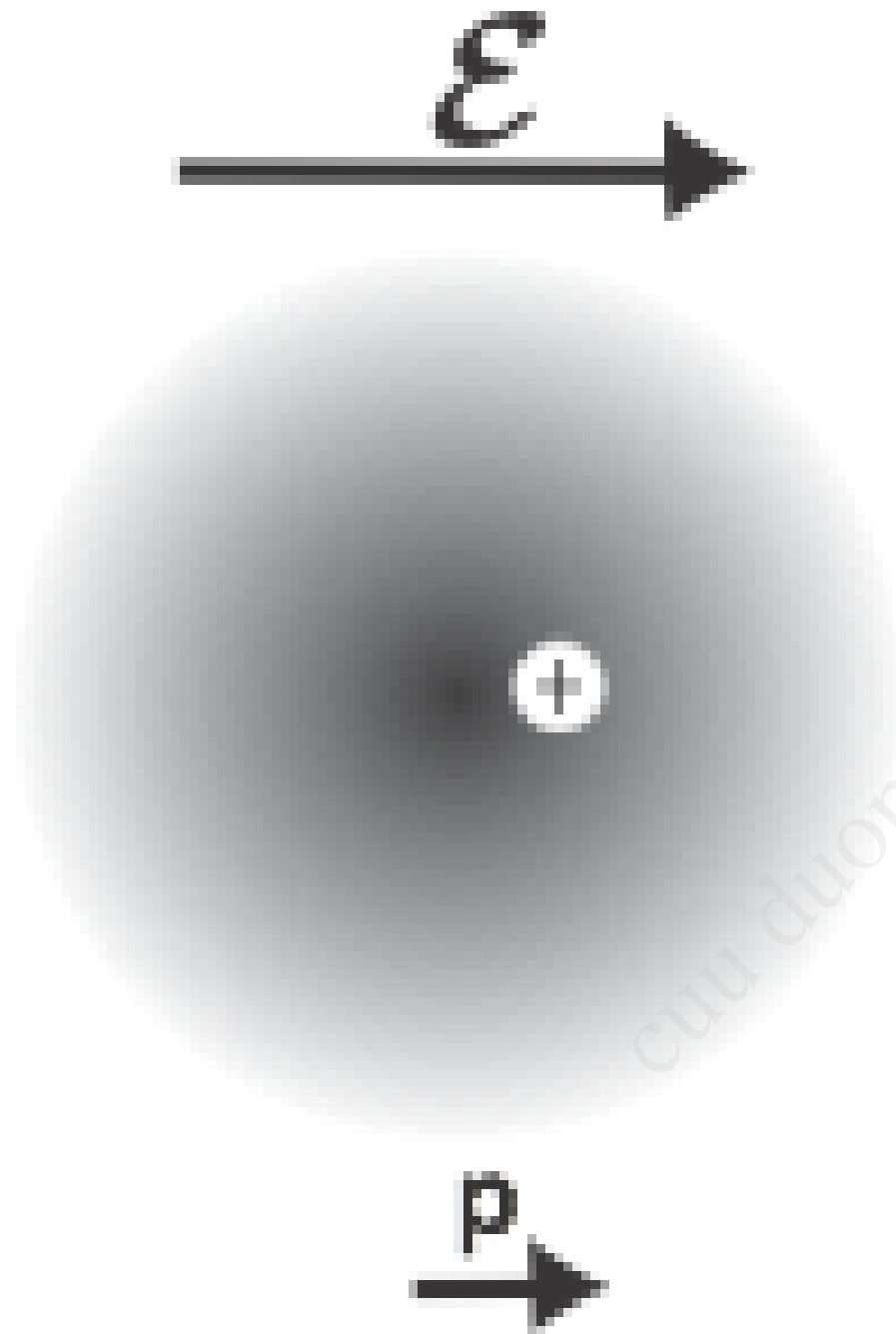
Microscopic origin: electronic polarization

for one atom

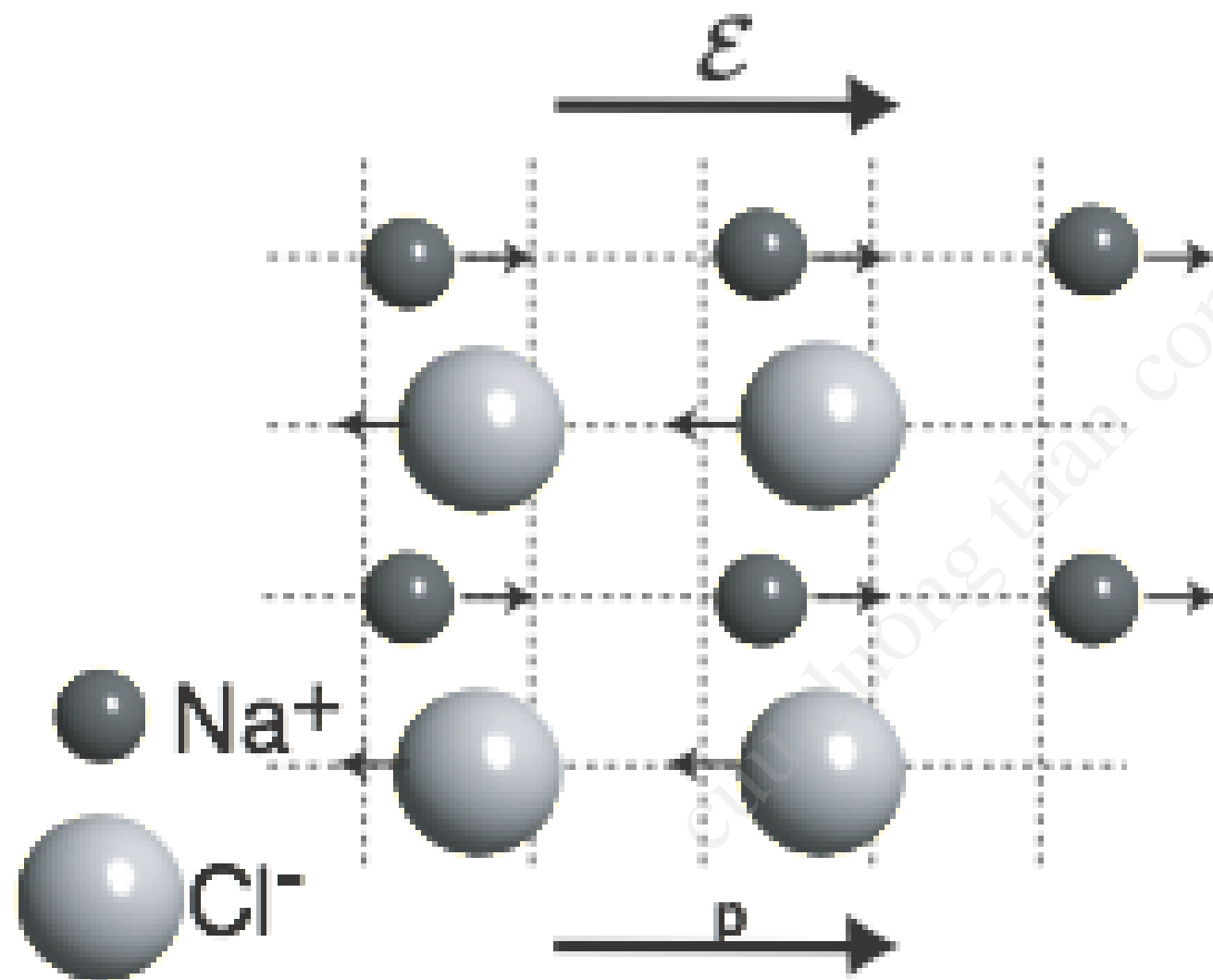
$$\mathbf{p} = \alpha \boldsymbol{\varepsilon}$$

for the solid

$$\mathbf{P} = \frac{N}{V} q \delta = \frac{N}{V} \mathbf{p}$$

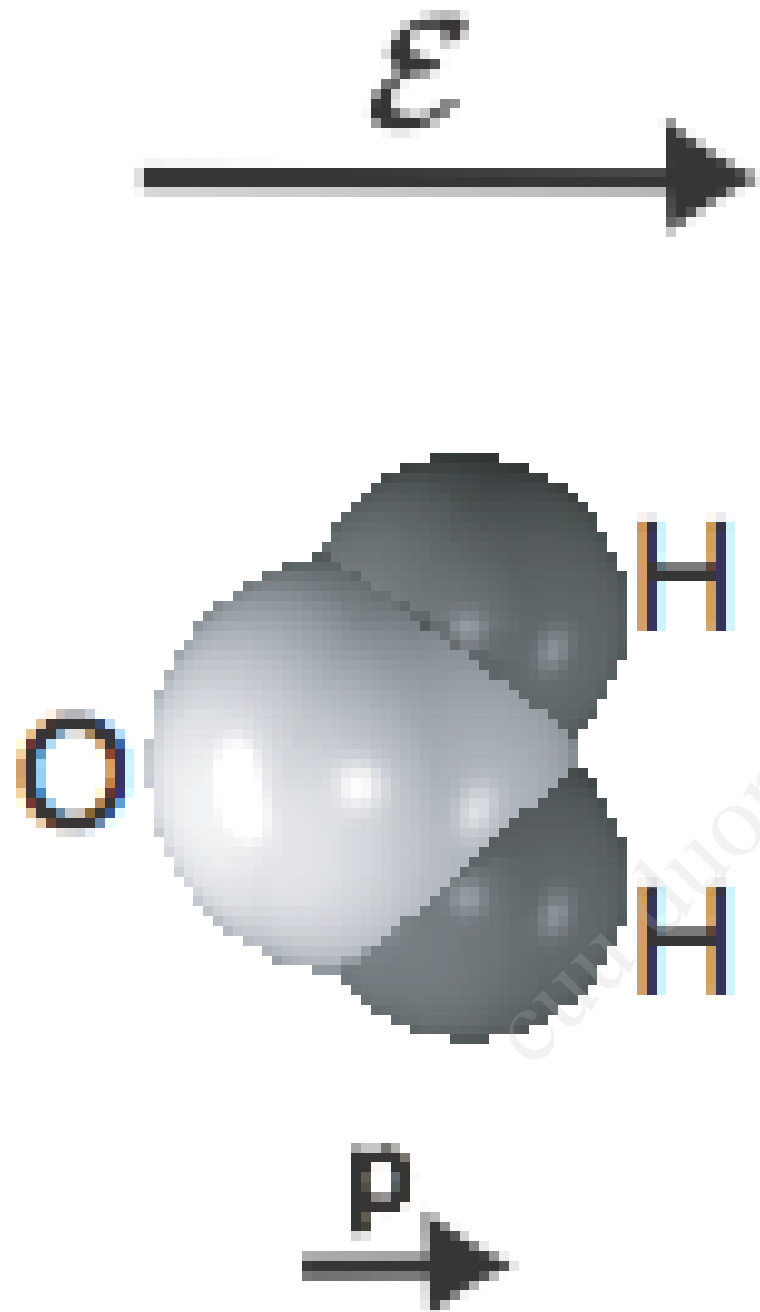


Microscopic origin: ionic polarization



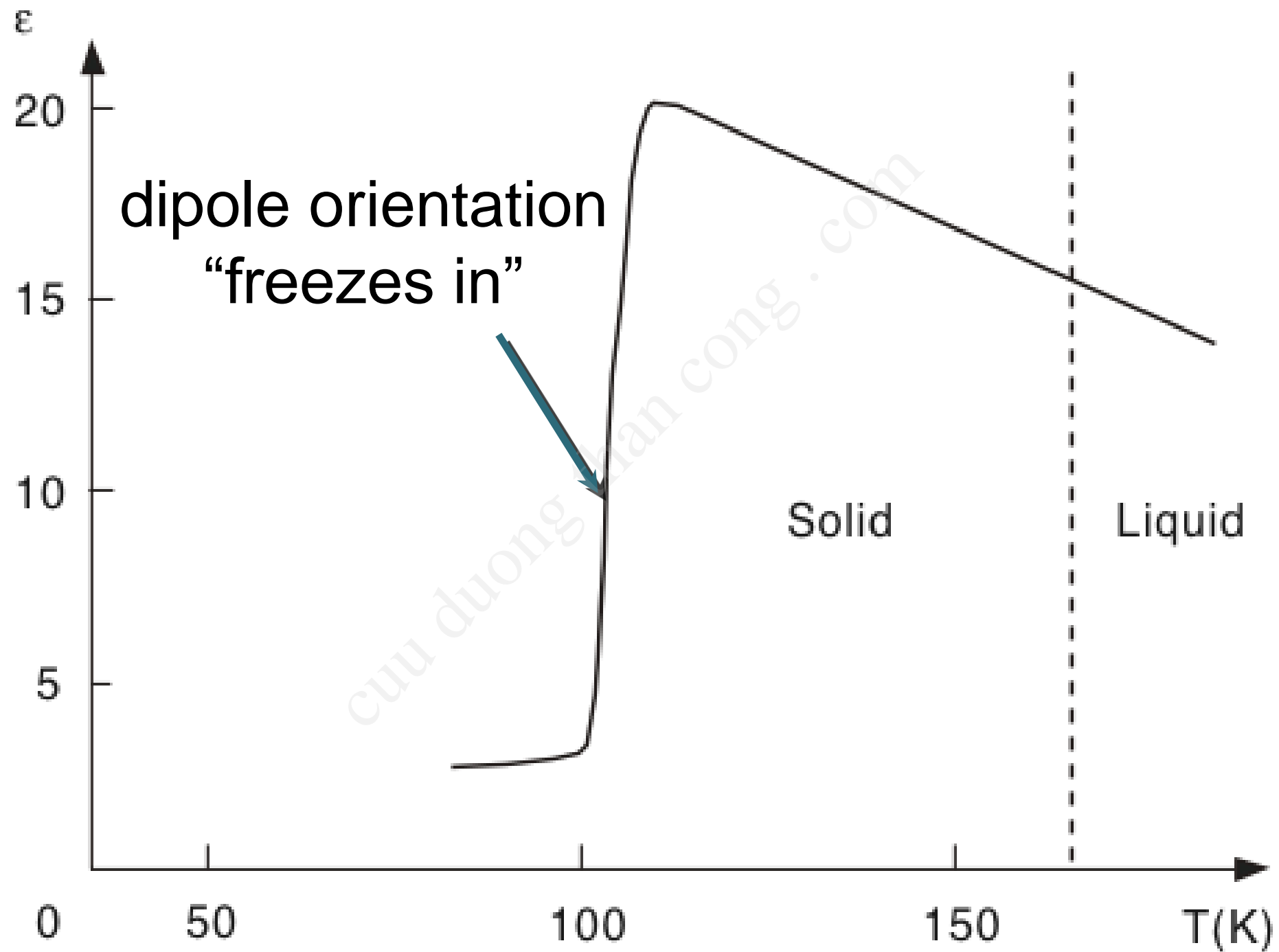
$$\mathbf{P} = \frac{N}{V} q \delta = \frac{N}{V} \mathbf{p}$$

Microscopic origin: orientational polarization



$$\mathbf{P} = \frac{N}{V} q \delta = \frac{N}{V} \mathbf{p}$$

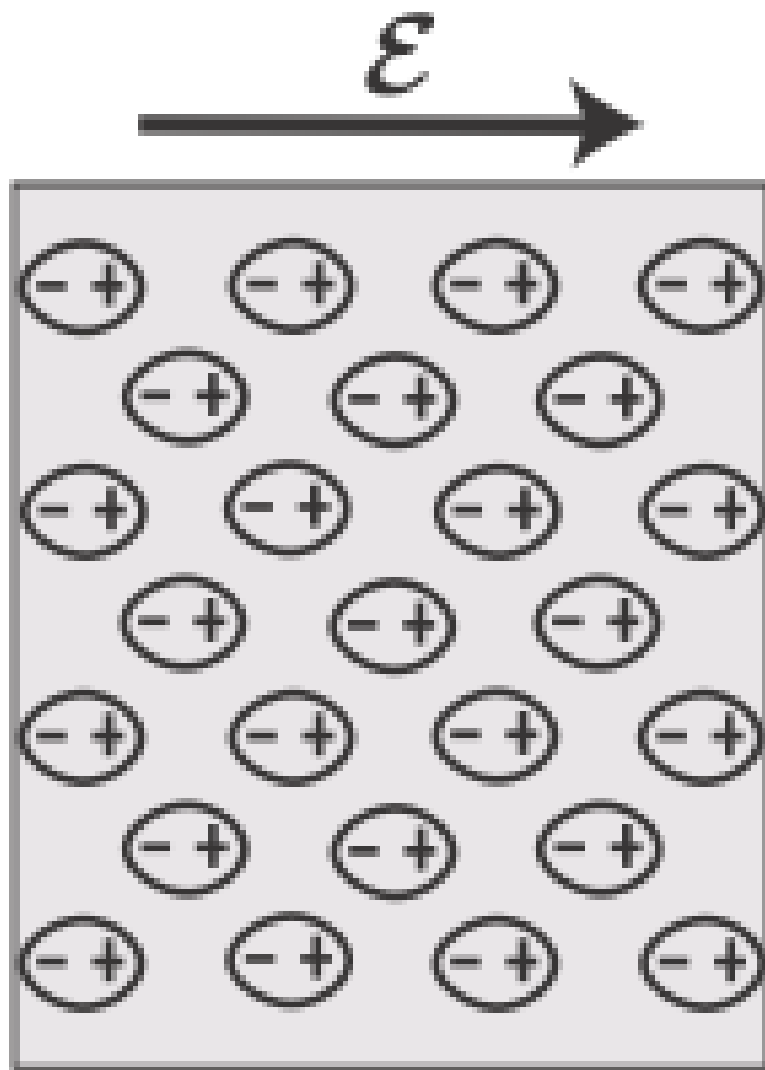
Example: Hydrogen chloride



The local field

From the measured ϵ can we figure out α ?

average field:
external plus internal



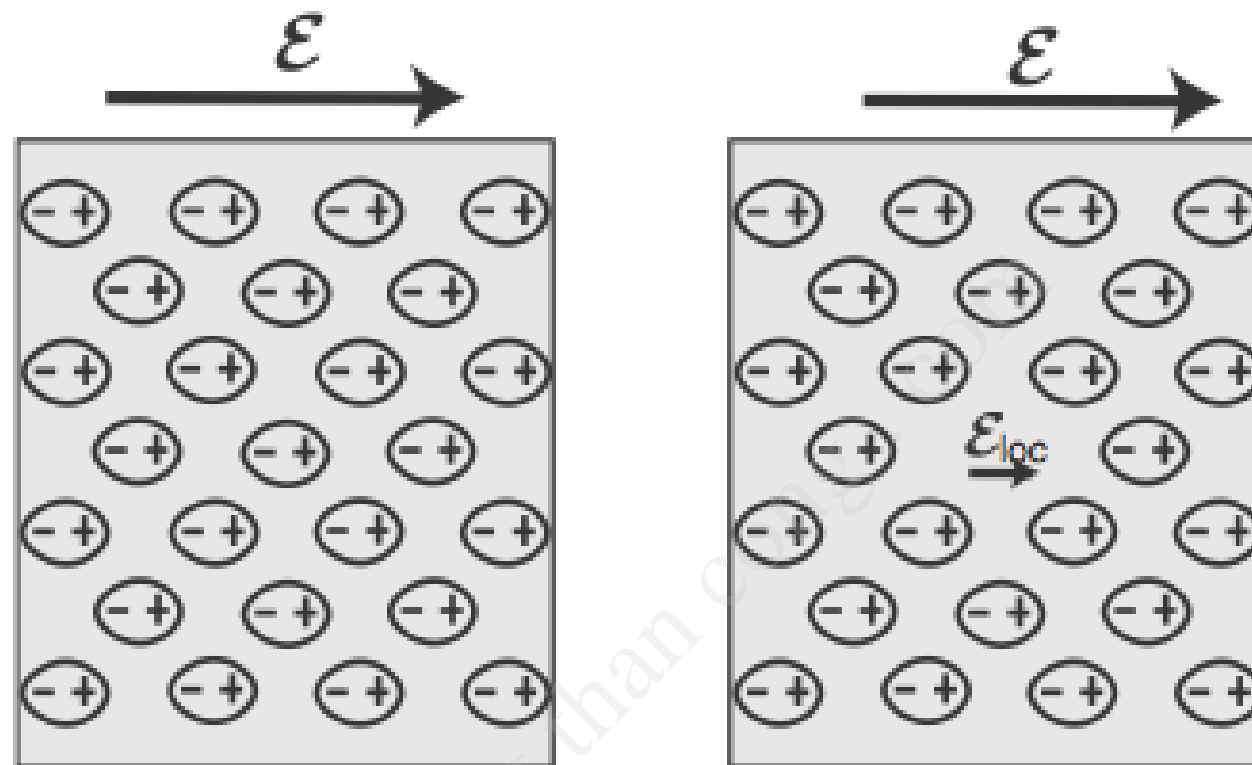
$$\mathbf{P} = (\epsilon - 1)\epsilon_0 \mathcal{E} = \frac{N}{V} \mathbf{p} = \frac{N}{V} \alpha \mathcal{E}$$

$$\alpha = \frac{(\epsilon - 1)\epsilon_0 V}{N}$$

simple but unfortunately also
incorrect!

The local field

What is the electric field each dipole 'feels' in a dielectric?



the actual local field is higher

$$\mathcal{E}_{\text{loc}} = \frac{1}{3}(\epsilon + 2)\mathcal{E}$$

$$\mathbf{P} = \frac{N}{V}\alpha\mathcal{E}_{\text{loc}} = \frac{N\alpha}{3V}(\epsilon + 2)\mathcal{E}$$

$$\mathbf{P} = (\epsilon - 1)\epsilon_0\mathcal{E}$$

Clausius-Mossotti relation

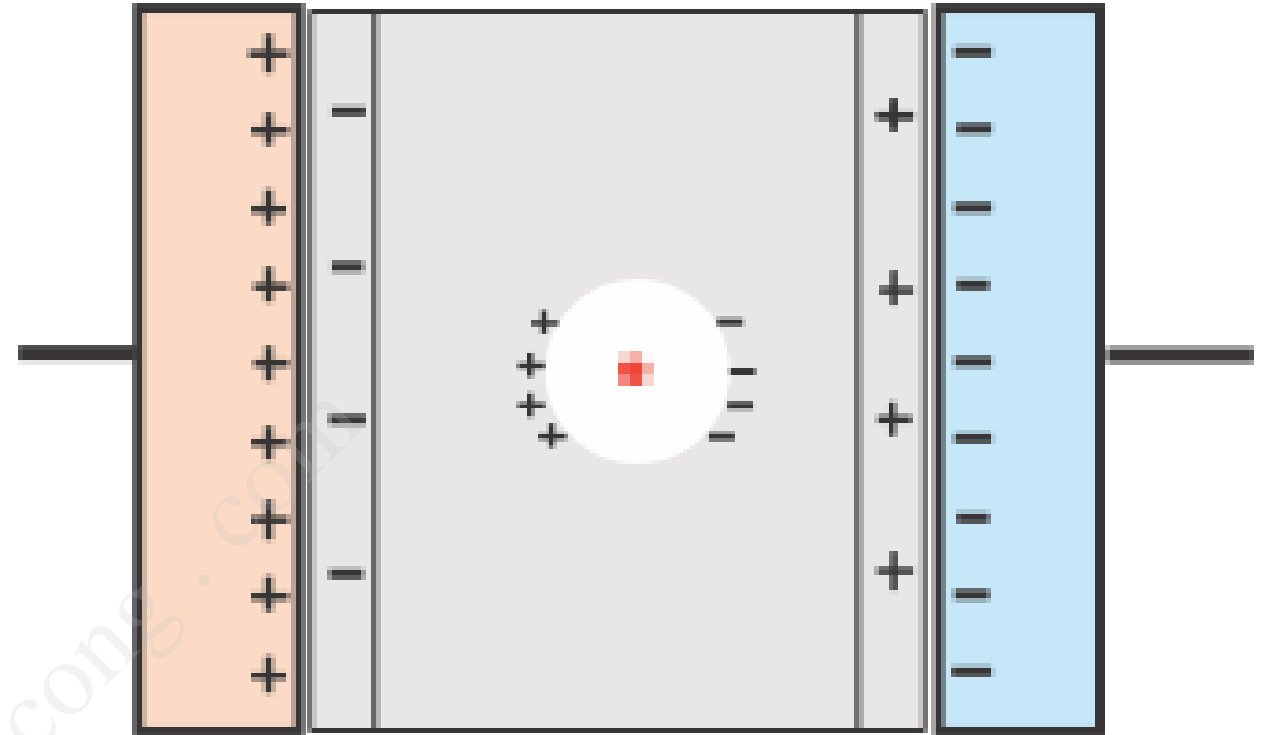
$$\alpha = \frac{\epsilon - 1}{\epsilon + 2} \frac{3\epsilon_0 V}{N}$$

(next few slides optional)

The local field at a point in the dielectric

field by external charges on plates \mathbf{E}_0

field by surface charges depolarization field \mathbf{E}_1



average macroscopic field $\mathbf{E} = \mathbf{E}_0 + \mathbf{E}_1$

field from the surface dipoles of a spherical cavity large against microscopic dimensions \mathbf{E}_2

field from inside this cavity \mathbf{E}_3

total local field $\mathbf{E}_{loc} = \mathbf{E}_0 + \mathbf{E}_1 + \mathbf{E}_2 + \mathbf{E}_3 = \mathbf{E} + \mathbf{E}_2 + \mathbf{E}_3$

The local field at a point in the dielectric
 calculation of the cavity field
 (z is direction between plates)

$$\mathbf{E}_2 = \int \frac{1}{4\pi\epsilon_0} \frac{\sigma}{r^2} \hat{\mathbf{r}} dS$$

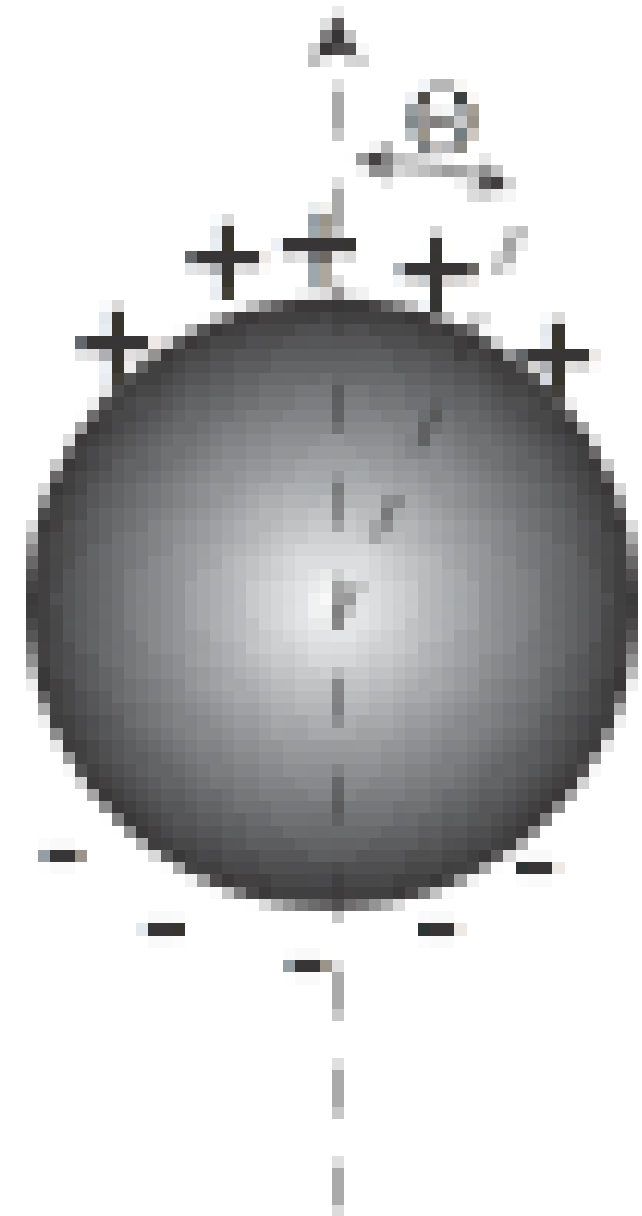
in z direction

$$E_2 = \int \frac{1}{4\pi\epsilon_0} \frac{\sigma}{r^2} \cos \Theta dS$$

surface charge density on sphere

$$\sigma = P \cos \Theta$$

$$E_2 = \int \frac{1}{4\pi\epsilon_0} \frac{P \cos \Theta}{r^2} \cos \Theta dS = \int_0^{2\pi} \int_0^\pi \frac{1}{4\pi\epsilon_0} \frac{P \cos \Theta}{r^2} \cos \Theta r^2 \sin \Theta d\phi d\Theta = \frac{1}{3\epsilon_0} P$$

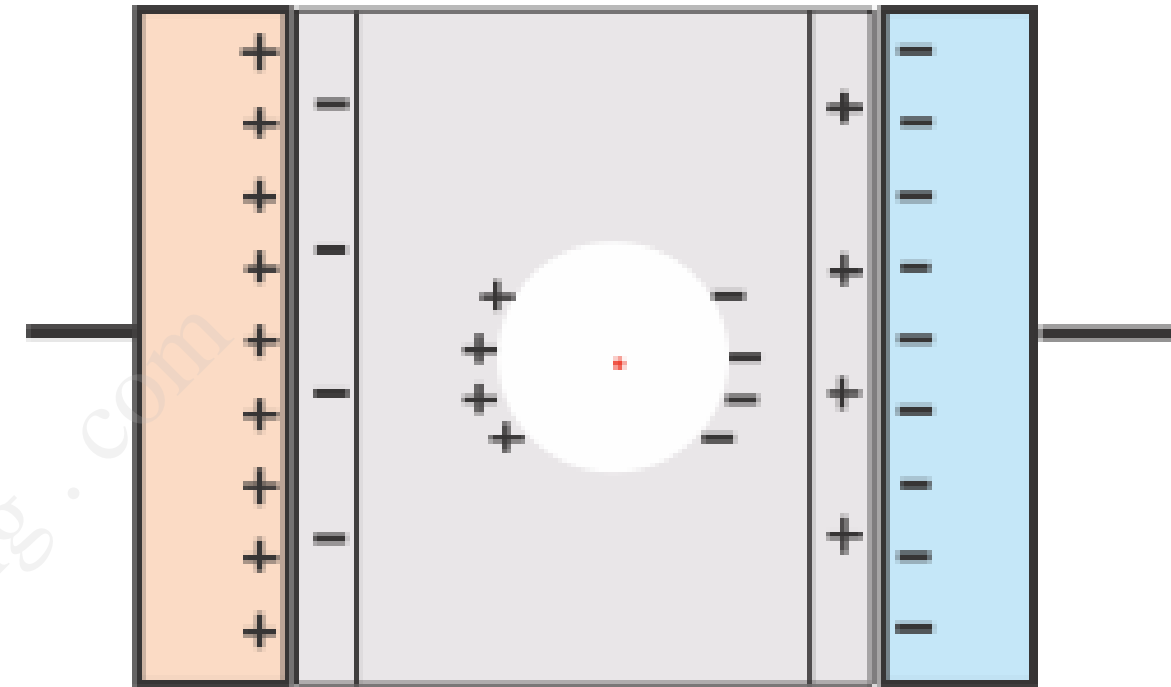


The local field at a point in the dielectric

calculation of the field
inside the cavity for a cubic lattice
field of a dipole (along z)

$$\mathbf{E}(\mathbf{r}) = \frac{3(\mathbf{p} \cdot \mathbf{r})\mathbf{r} - r^2\mathbf{p}}{4\pi\epsilon_0 r^5}$$

$$E_z(r) = p \frac{3z^2 - r^2}{4\pi\epsilon_0 r^5}$$



field at centre for all dipoles in cavity

$$E_z(r) = p \sum_i \frac{3z_i^2 - r_i^2}{4\pi\epsilon_0 r_i^5} = p \sum_i \frac{2z_i^2 - x_i^2 - y_i^2}{4\pi\epsilon_0 r_i^5} = 0$$

$$\sum_i \frac{z_i^2}{r_i^5} = \sum_i \frac{x_i^2}{r_i^5} = \sum_i \frac{y_i^2}{r_i^5}$$

The local field at a point in the dielectric

calculation of the total
local field

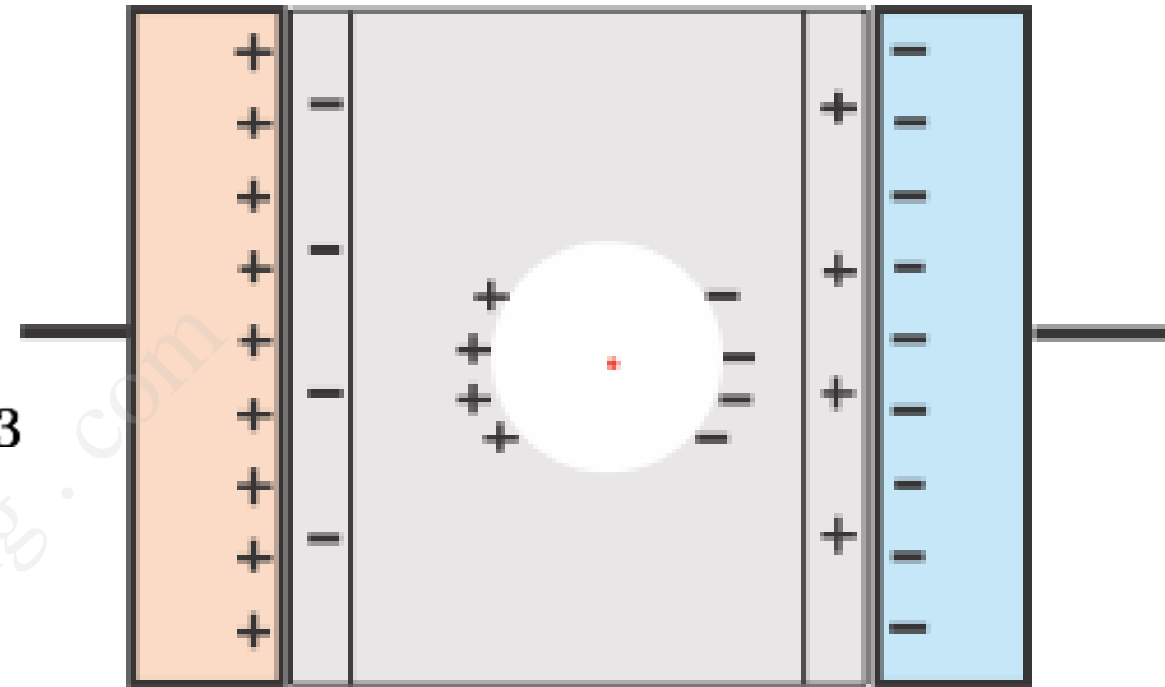
$$\mathbf{E}_{loc} = \mathbf{E}_0 + \mathbf{E}_1 + \mathbf{E}_2 + \mathbf{E}_3 = \mathbf{E} + \mathbf{E}_2 + \mathbf{E}_3$$

$$= \mathbf{E} + \frac{1}{3\epsilon_0} \mathbf{P}$$

$$\mathbf{P} = (\epsilon - 1)\epsilon_0 \mathbf{E}$$

it follows that

$$\mathbf{E}_{loc} = \frac{1}{3}(\epsilon + 2)\mathbf{E}$$



(end of optional slides)

The dielectric constant

material	dielectric constant ϵ
vacuum	1
air	1.000576 (283 K, 1013 hPa)
rubber	2.5 - 3.5
glass	5-10
NaCl	5.9
ethanol	25.8
water	81.1
strontium titanate	350

Clausius-Mossotti relation

or

$$\alpha = \frac{\epsilon - 1}{\epsilon + 2} \frac{3\epsilon_0 V}{N}$$

$$\epsilon = \frac{3\epsilon_0 V/N + 2\alpha}{3\epsilon_0 V/N - \alpha}$$

Frequency dependence of the dielectric constant

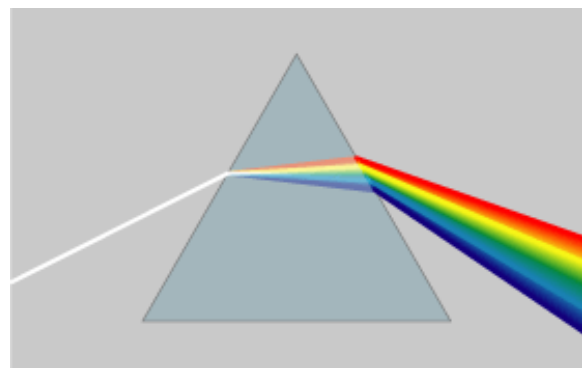
plane wave

$$\mathcal{E}(z, t) = \mathcal{E}_0 e^{i(kz - \omega t)}$$

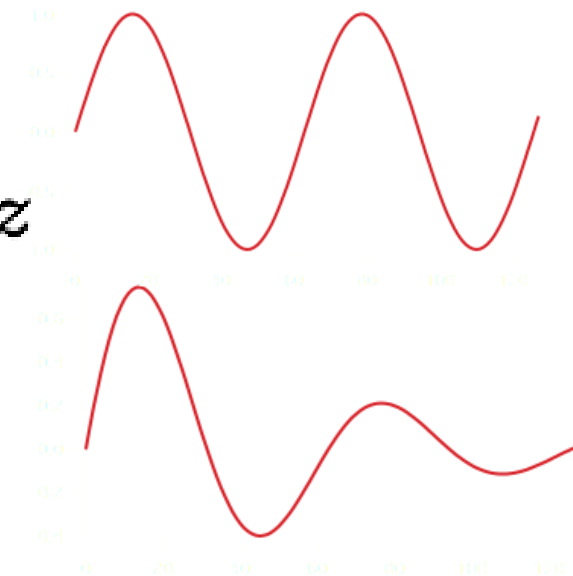
$$k = \frac{2\pi N}{\lambda_0}$$

complex index
of refraction

$$N = n + i\kappa$$



$$\mathcal{E}(z, t) = \mathcal{E}_0 e^{i\left(\frac{2\pi n}{\lambda_0} z - \omega t\right)} e^{-\frac{2\pi \kappa}{\lambda_0} z}$$



Maxwell relation

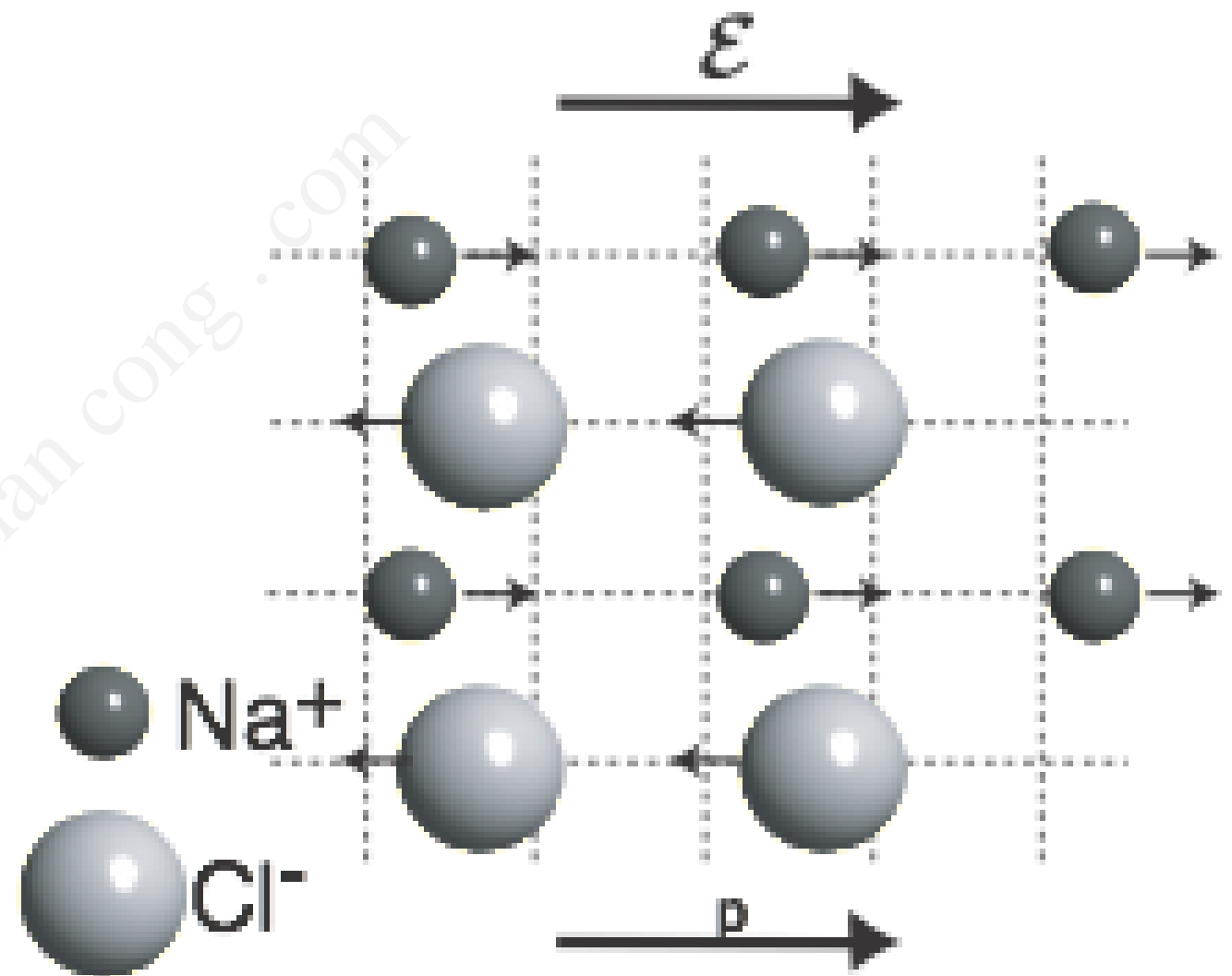
$$N = \sqrt{\epsilon} = \sqrt{\epsilon_r + i\epsilon_i}$$

$$\mathcal{E}(z, t) = \mathcal{E}_0 e^{i((2\pi N/\lambda_0)z - \omega t)} = \mathcal{E}_0 e^{i((\omega\sqrt{\epsilon}/c)z - \omega t)}$$

all the interesting physics is in the dielectric function!

Frequency dependence of the dielectric constant

- Slowly varying fields: quasi-static behaviour.
- Fast varying fields: polarisation cannot follow anymore (only electronic polarization can).
- Of particular interest is the optical regime.



Frequency dependence of the dielectric constant

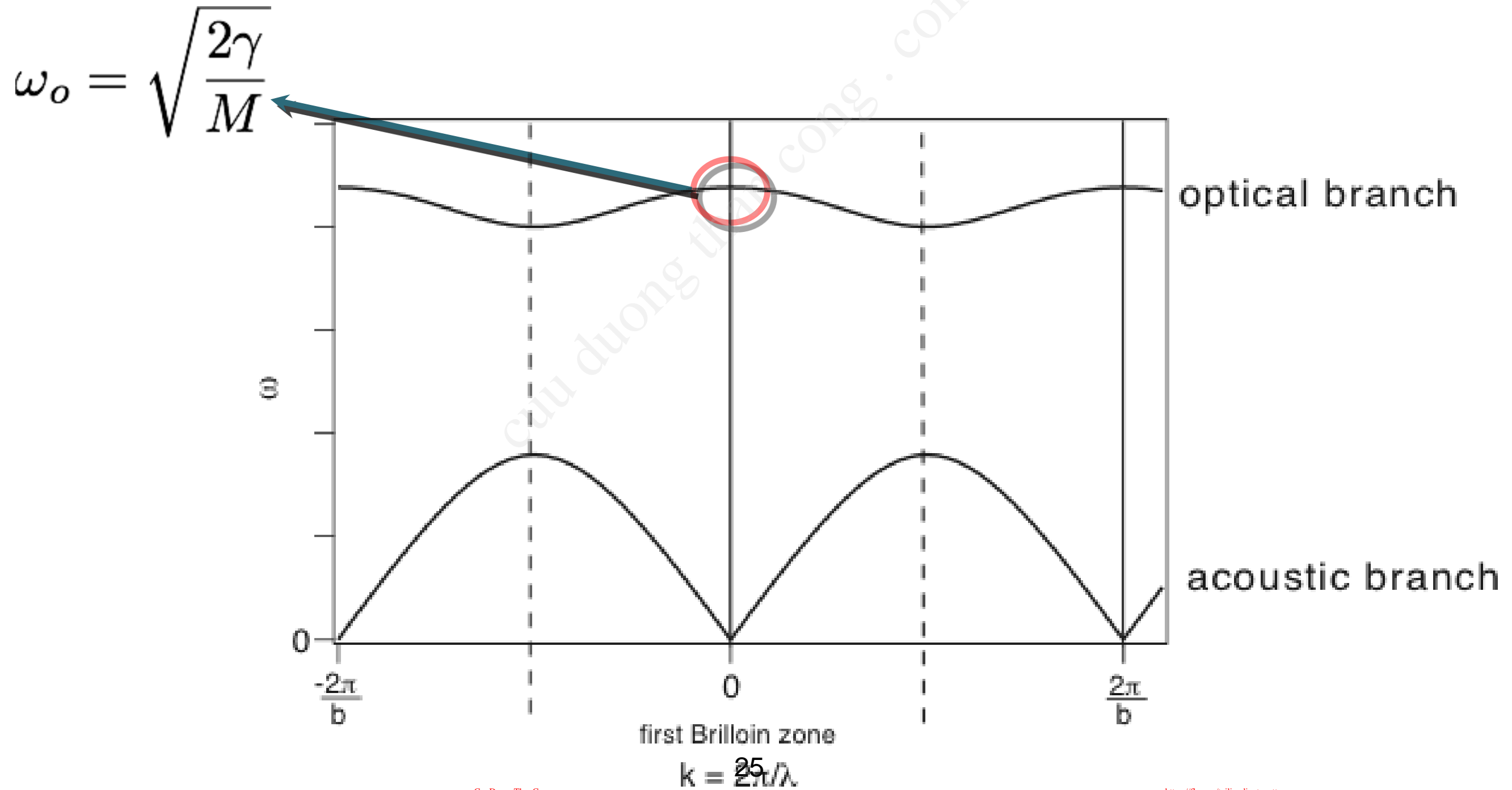
- Slowly varying fields: quasi-static behaviour.
- Fast varying fields: polarisation cannot follow anymore (only electronic).
- Of particular interest is the optical regime.

material	static ϵ	ϵ_{opt}
diamond	5.68	5.66
NaCl	5.9	2.34
LiCl	11.95	2.78
TiO ₂	94	6.8
quartz	3.85	2.13

Frequency dependence of the dielectric constant: driven and damped harmonic motion

- We obtain an expression for the frequency-dependent dielectric function as given by the polarization of the lattice.
- The lattice motion is just described as one harmonic oscillator.


light E-field
 (almost constant over very long distance)



Frequency dependence of the dielectric constant: driven and damped harmonic motion

we start with the usual differential equation


$$\frac{d^2 x}{dt^2} + \eta \frac{dx}{dt} + \omega_0^2 x = \frac{e\mathcal{E}_0}{M} e^{-i\omega t}$$



friction
term



harmonic
restoring
term



driving
field
(should be
local field)

$$\omega_0 = \sqrt{\frac{2\gamma}{M}}$$

Frequency dependence of the dielectric constant: driven and damped harmonic motion

$$\frac{d^2x}{dt^2} + \eta \frac{dx}{dt} + \omega_0^2 x = \frac{e\mathcal{E}_0}{M} e^{-i\omega t}$$

solution $x = Ae^{-i\omega t}$

$$A = \frac{e\mathcal{E}_0}{M} \frac{1}{\omega_0^2 - \omega^2 - i\eta\omega}$$

$$A = \frac{e\mathcal{E}_0}{M} \left(\frac{\omega_0^2 - \omega^2}{(\omega_0^2 - \omega^2)^2 + \eta^2\omega^2} + \frac{i\eta\omega}{(\omega_0^2 - \omega^2)^2 + \eta^2\omega^2} \right)$$

real part

imaginary part

Frequency dependence of the dielectric constant: driven and damped harmonic motion

$$P(t) = P_i(t) + P_e(t) = \frac{N}{V} e A e^{-i\omega t} + \frac{N}{V} \alpha \mathcal{E}_0 e^{-i\omega t}$$

ionic / lattice part

electronic / atomic part

$$\epsilon = \frac{P(t)}{\epsilon_0 \mathcal{E}_0 e^{-i\omega t}} + 1 = \frac{N e A}{V \epsilon_0 \mathcal{E}_0} + \frac{N \alpha}{V \epsilon_0} + 1$$

for sufficiently high frequencies we know that

$$P_i = 0$$

$$\epsilon_{\text{opt}} = \frac{N \alpha}{V \epsilon_0} + 1$$

$$\epsilon(\omega) = \frac{N e A}{V \epsilon_0 \mathcal{E}_0} + \epsilon_{\text{opt}}$$

Frequency dependence of the dielectric constant: driven and damped harmonic motion

combine

$$\epsilon(\omega) = \frac{NeA}{V\epsilon_0\mathcal{E}_0} + \epsilon_{\text{opt}}$$

with

$$A = \frac{e\mathcal{E}_0}{M} \left(\frac{\omega_0^2 - \omega^2}{(\omega_0^2 - \omega^2)^2 + \eta^2\omega^2} + \frac{i\eta\omega}{(\omega_0^2 - \omega^2)^2 + \eta^2\omega^2} \right)$$

to get the complex dielectric function to be

$$\epsilon = \epsilon_r + i\epsilon_i$$

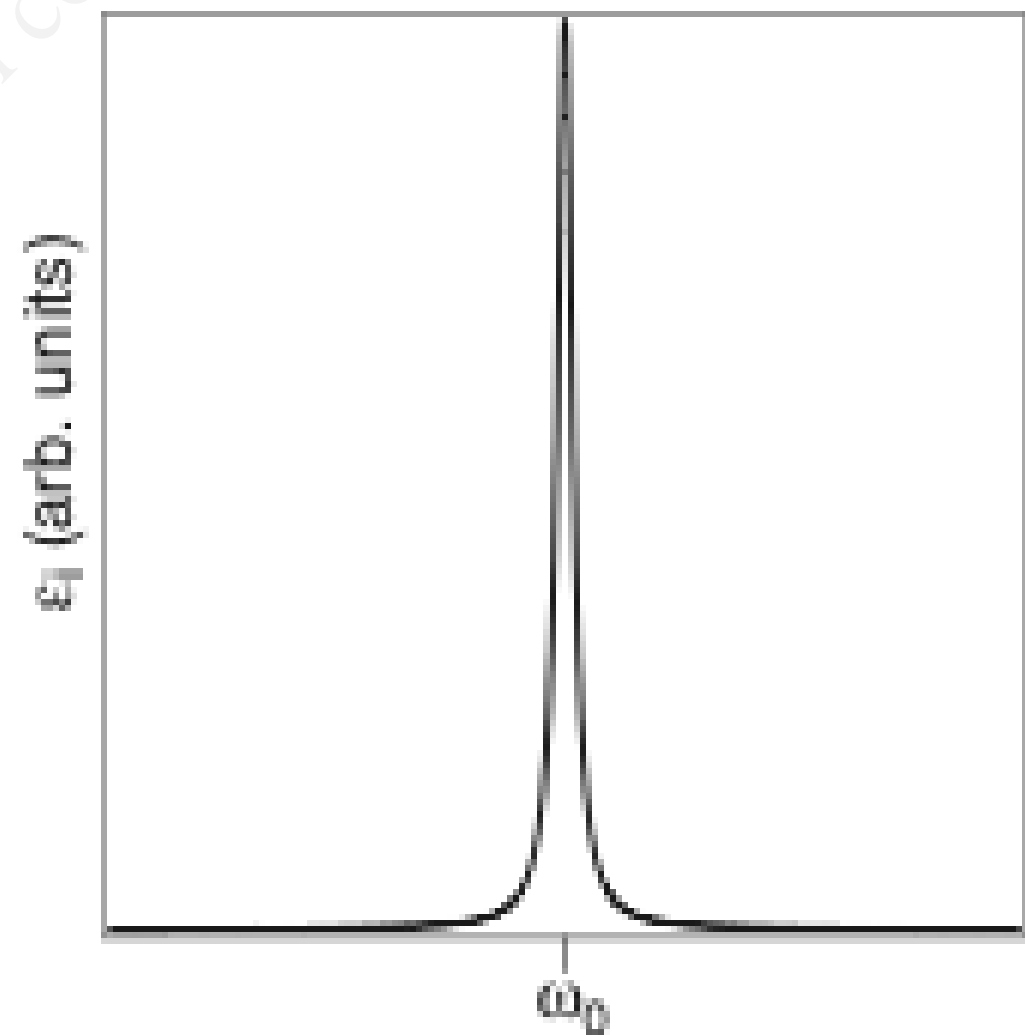
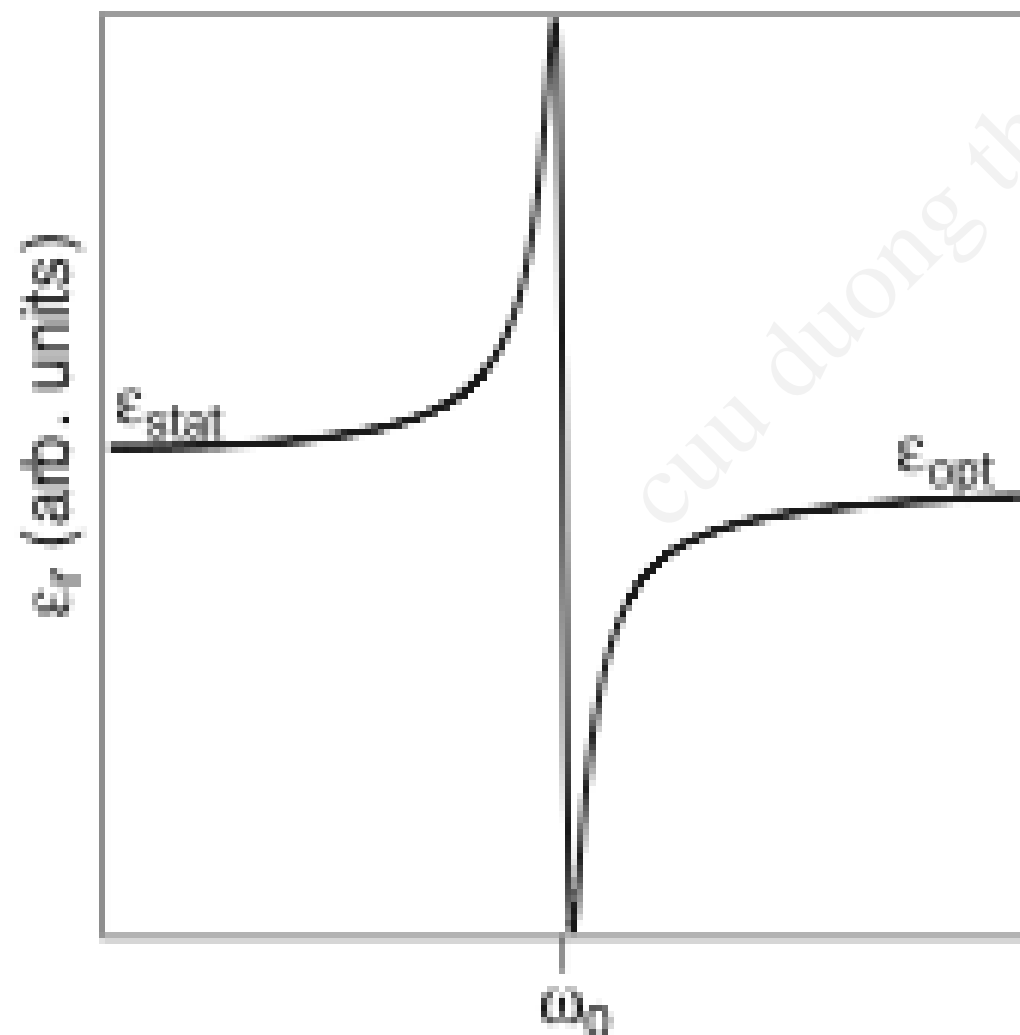
$$\epsilon_r(\omega) = \frac{Ne^2}{V\epsilon_0M} \frac{\omega_0^2 - \omega^2}{(\omega_0^2 - \omega^2)^2 + \eta^2\omega^2} + \epsilon_{\text{opt}}$$

$$\epsilon_i(\omega) = \frac{Ne^2}{V\epsilon_0M} \frac{\eta\omega}{(\omega_0^2 - \omega^2)^2 + \eta^2\omega^2}$$

Frequency dependence of the dielectric constant: driven and damped harmonic motion

$$\epsilon = \epsilon_r + i\epsilon_i$$

$$\epsilon_r = \frac{Ne^2}{V\epsilon_0 m} \frac{\omega_0^2 - \omega^2}{(\omega_0^2 - \omega^2)^2 + \eta^2 \omega^2} + \epsilon_{opt} \quad \epsilon_i = \frac{Ne^2}{V\epsilon_0 m} \frac{\eta \omega}{(\omega_0^2 - \omega^2)^2 + \eta^2 \omega^2}$$



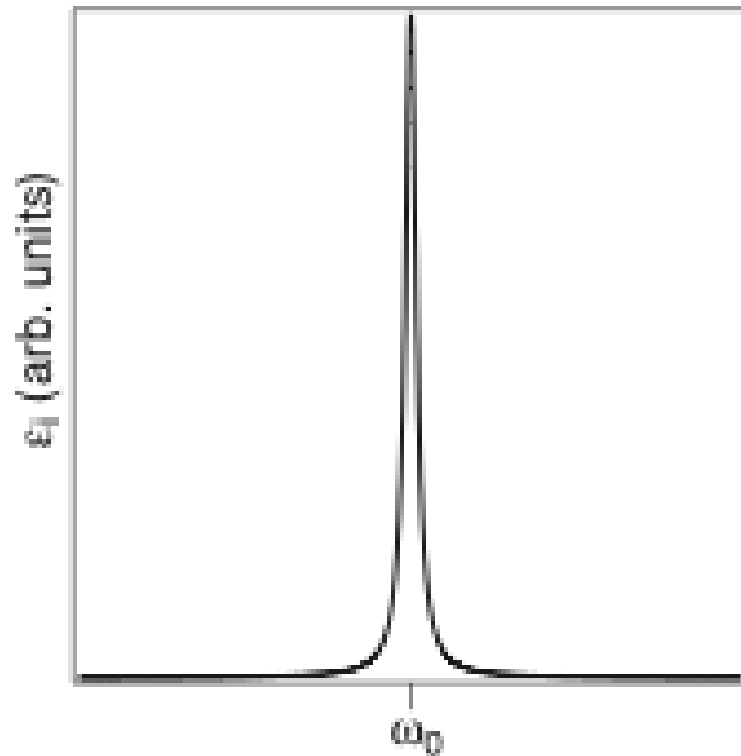
remember the plasma oscillation in a metal:
even higher frequencies

values for the plasma energy $\hbar\omega_P$

	measured	calculated
K	3.72 eV	4.29 eV
Mg	10.6 eV	10.9 eV
Al	15.3 eV	15.8 eV
Si	16.6 eV	16.0 eV
Ge	16.2 eV	16.0 eV

- We have seen that metals are transparent above the plasma frequency (in the UV).
- This lends itself to a simple interpretation: above the plasma frequency the electrons cannot keep up with the rapidly changing field and therefore they cannot keep the metal field-free, like they do in electrostatics.

The meaning of ϵ_i



instantaneous power dissipation (per unit volume)

$$p(t) = j(t)\mathcal{E}(t)$$

use

$$\mathcal{E}(t) = \mathcal{E}_0 \exp(-i\omega t) \quad \mathbf{j} = \text{curl} \mathbf{H} - \frac{\partial \mathbf{D}}{\partial t}$$

$$j(t) = -\frac{\partial D}{\partial t} = -\frac{\partial}{\partial t} \epsilon \epsilon_0 \mathcal{E}(t) = \epsilon_0 \mathcal{E}(t) \left(i\omega \epsilon_r - \omega \epsilon_i \right)$$

on average the dissipated power is

$$\bar{p} = \frac{1}{T} \int_0^T \mathcal{E}(t) j(t) dt$$

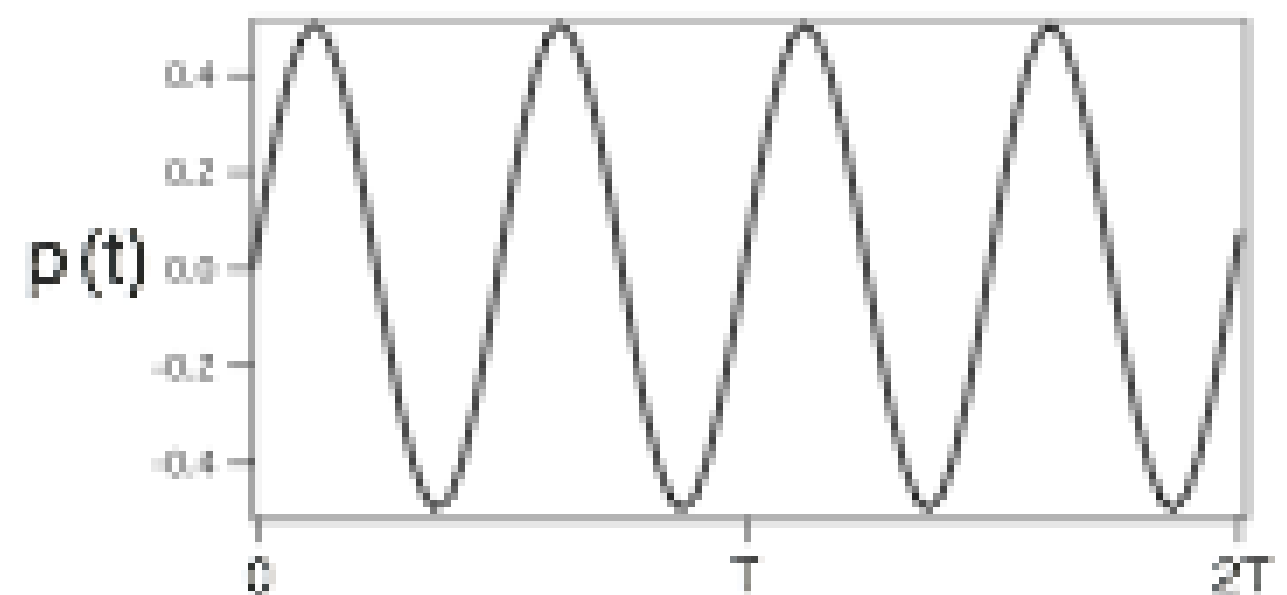
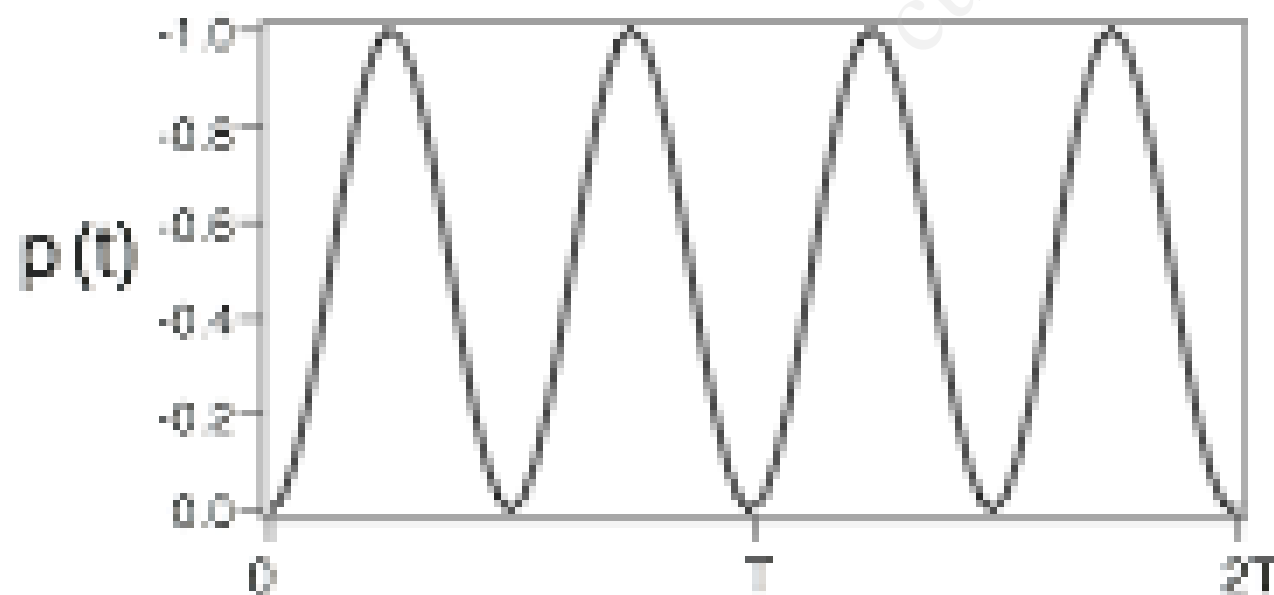
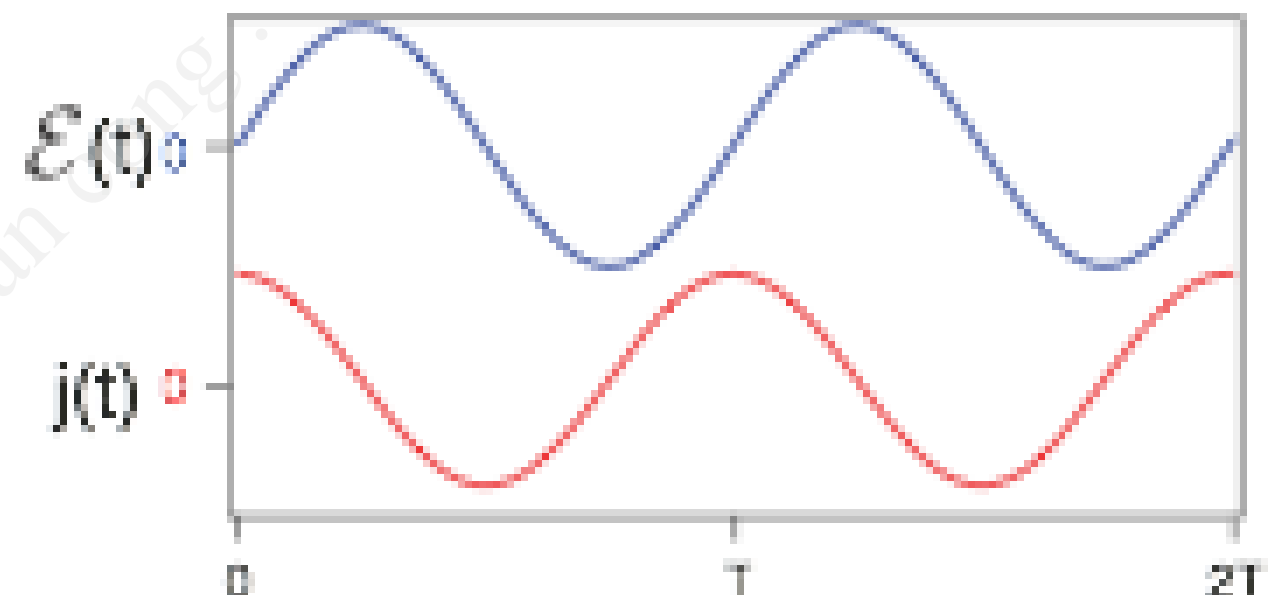
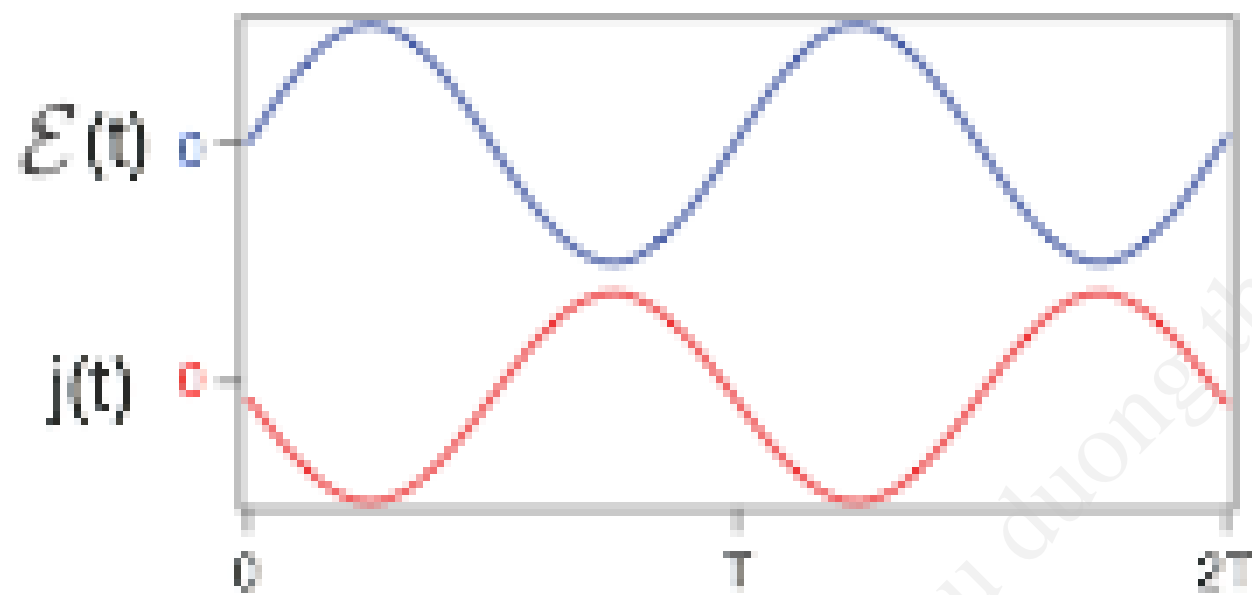
$$j(t) = \epsilon_0 \mathcal{E}(t) \left(i\omega\epsilon_r - \omega\epsilon_i \right)$$

energy
dissipation

$$\bar{p} = \frac{1}{T} \int_0^T \mathcal{E}(t) j(t) dt$$

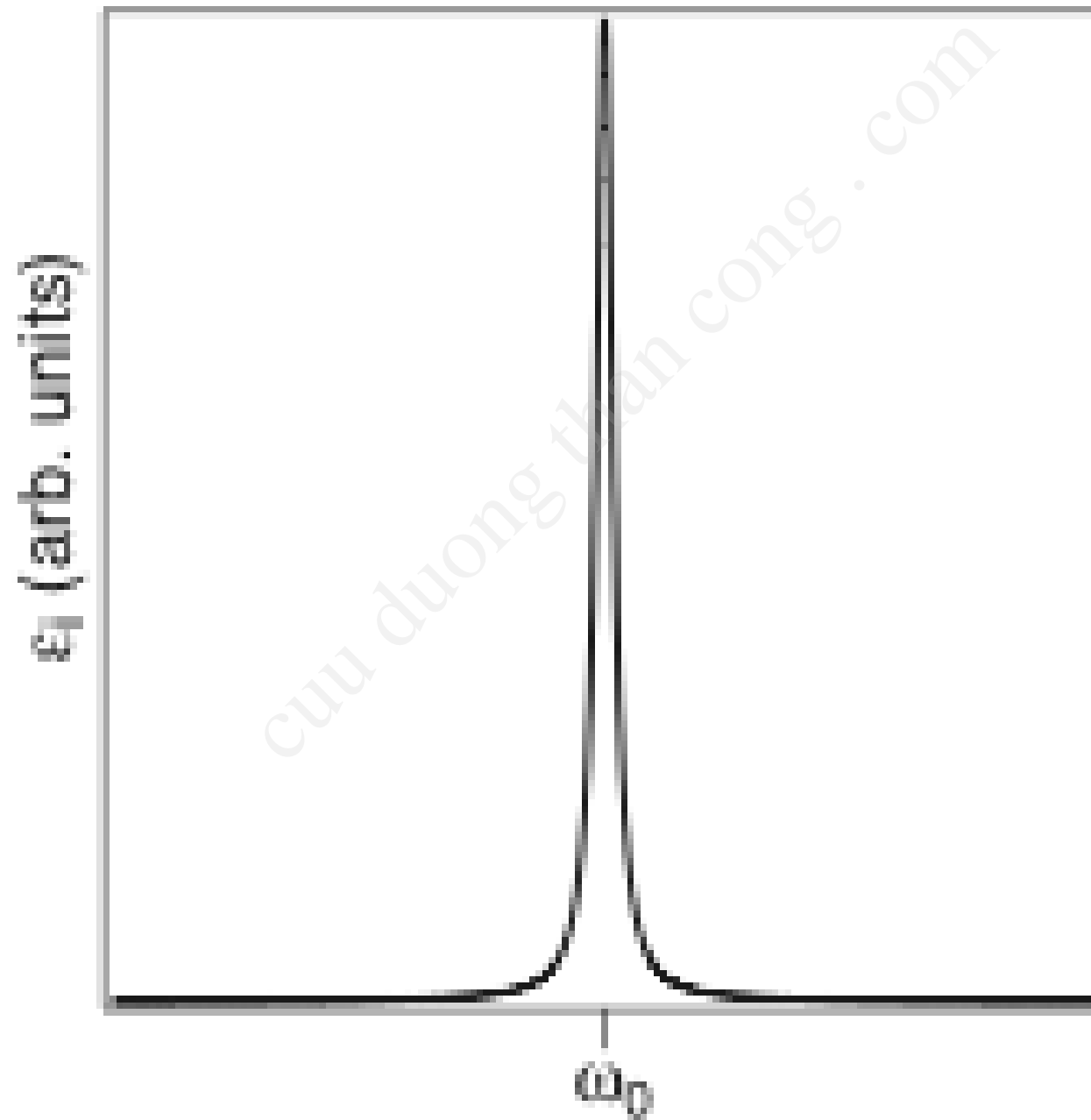
ϵ imaginary

ϵ real



The meaning of ε_i

energy dissipation



Frequency dependence of the dielectric constant: even higher frequencies (optical)



Si



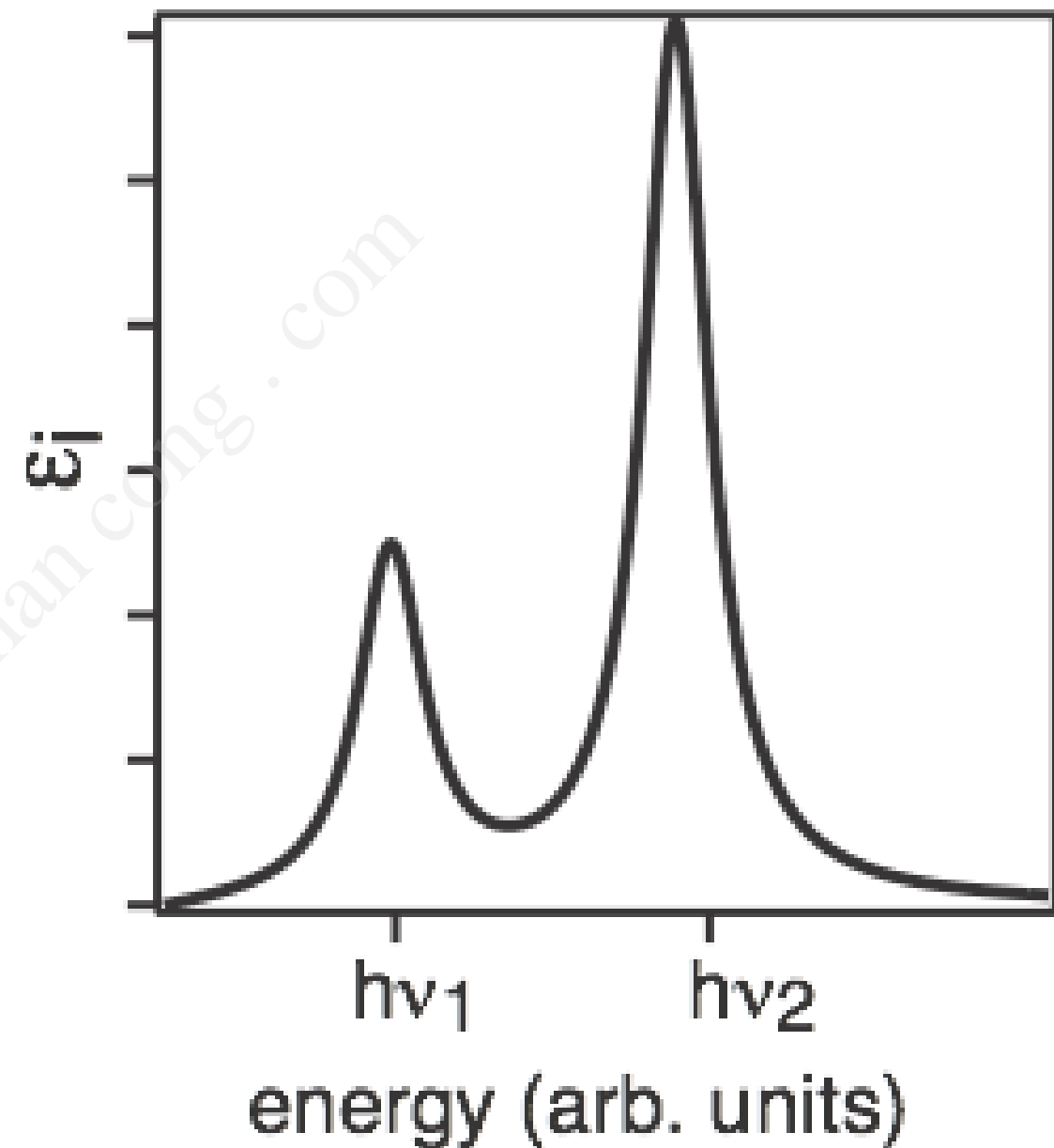
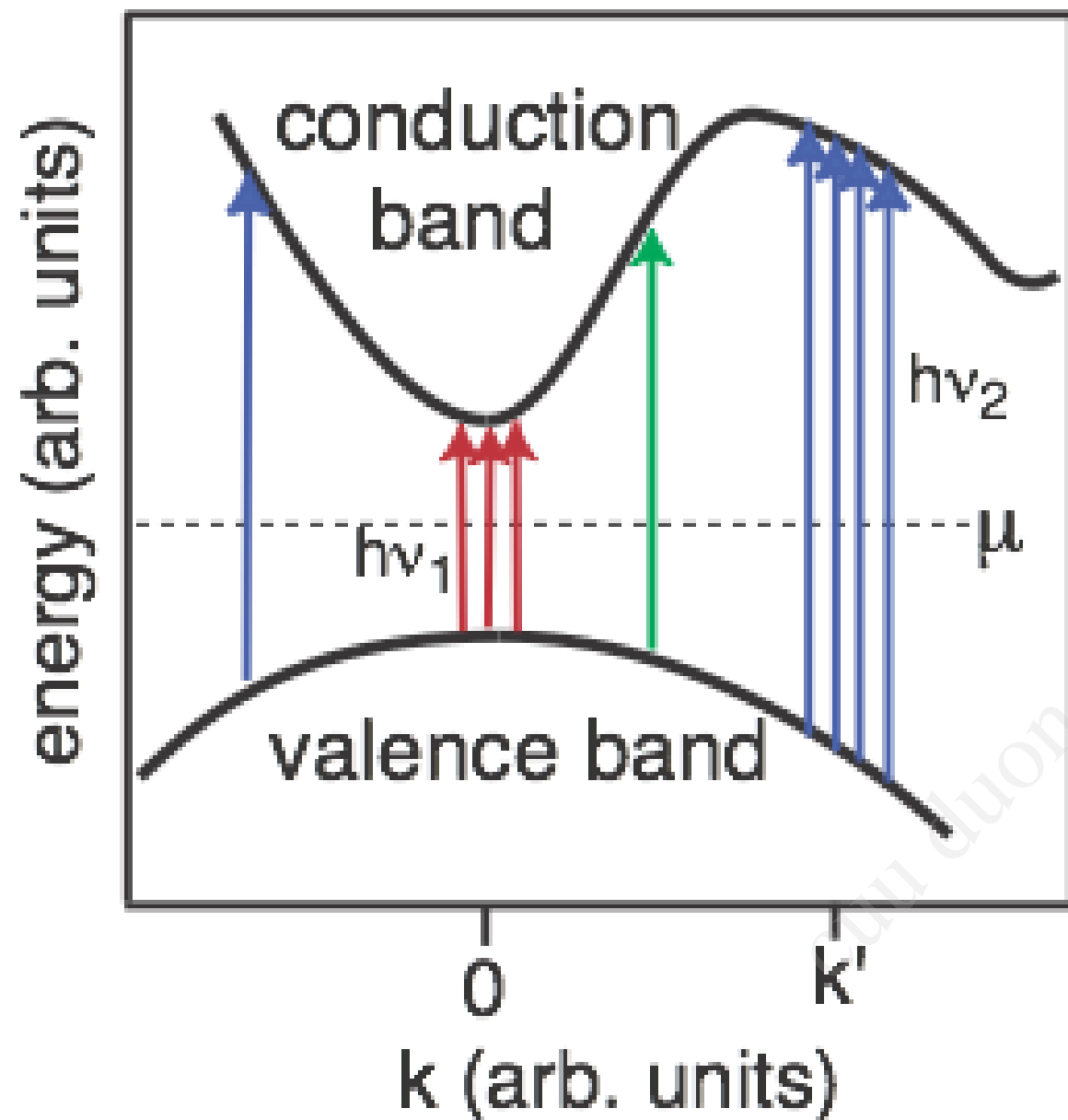
CdSe



CdS

image source: wikipedia (Si) and <http://woelen.homescience.net> (CdSe, CdS)

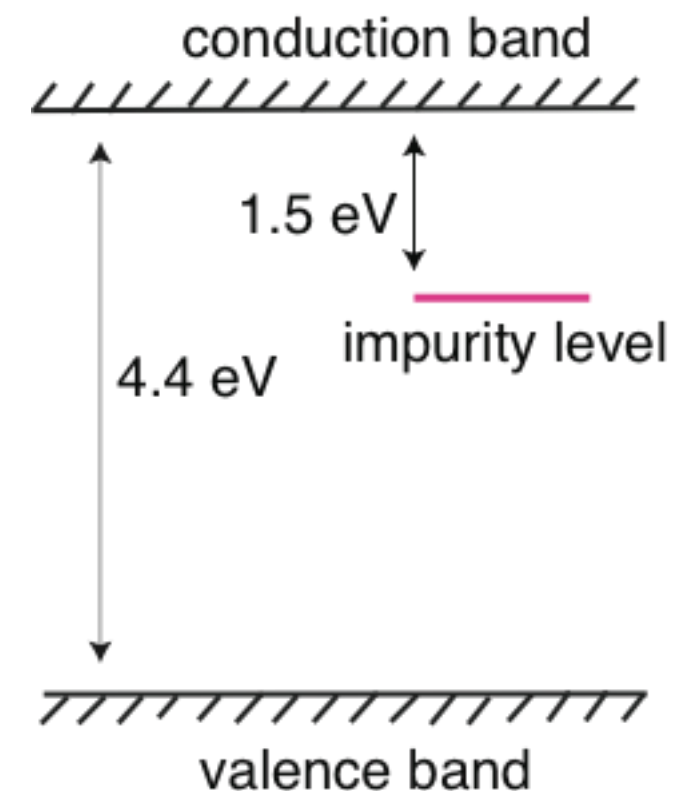
Frequency dependence of the dielectric constant: even higher frequencies (optical)



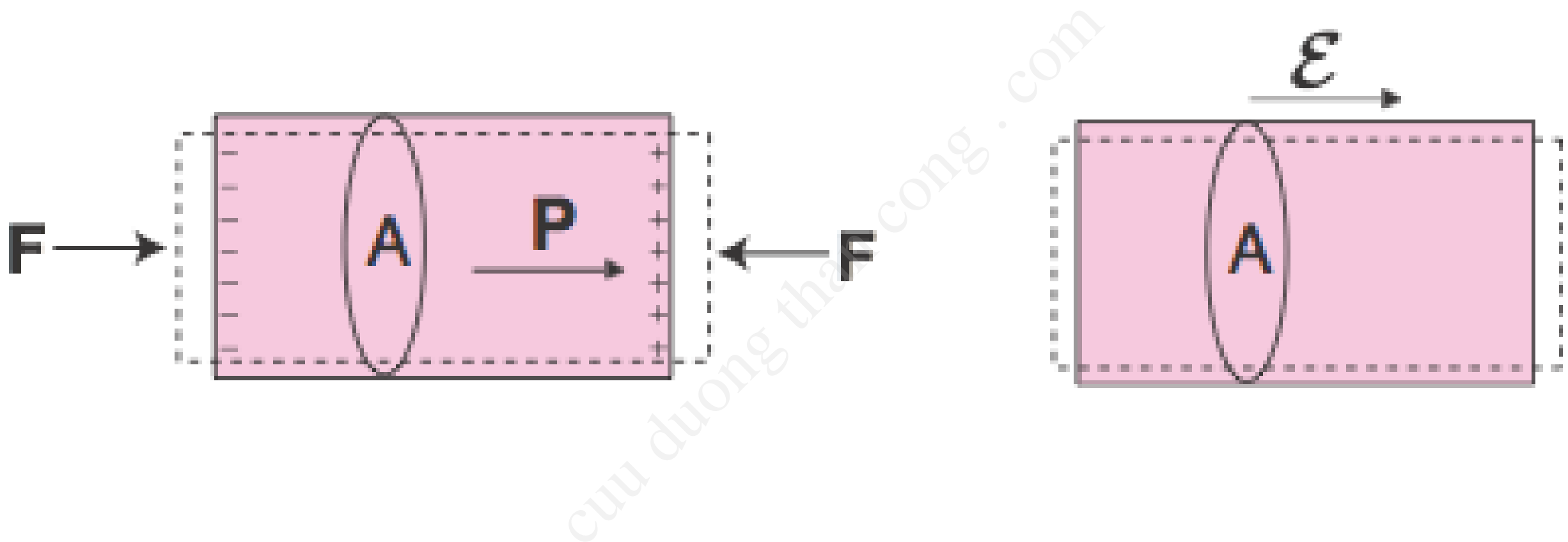
$$\epsilon_i(h\nu) \propto \sum_{\mathbf{k}} M^2 \delta(E_C(\mathbf{k}) - E_V(\mathbf{k}) - h\nu)$$

Impurities in dielectrics

- Single-crystals of wide-gap insulators are optically transparent (diamond, alumina)
- Impurities in the band gap can lead to absorption of light with a specific frequency
- Doping with shallow impurities can also lead to semiconducting behaviour of the dielectrics. This is favourable for high-temperature applications because one does not have to worry about intrinsic carriers (e.g. in the case of diamond or more likely SiC)



Piezoelectricity

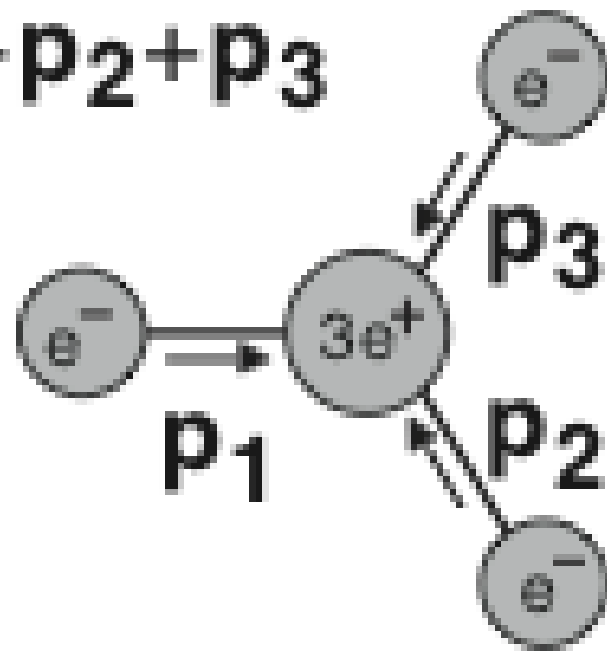


applying stress gives
rise to a polarization

applying an electric field
gives rise to strain

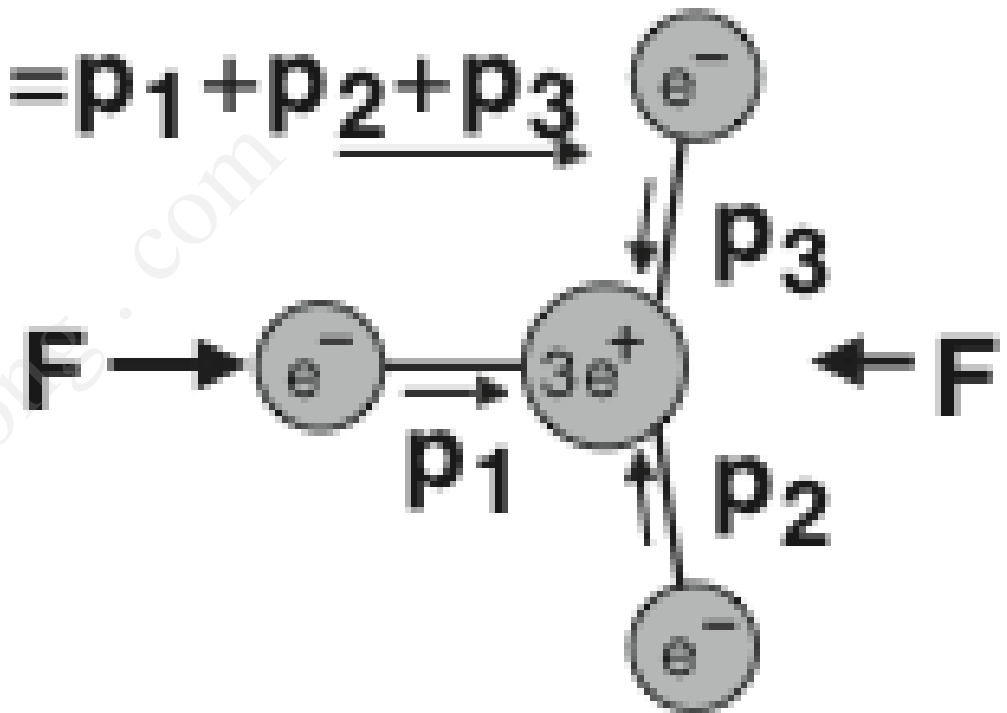
Piezoelectricity

$$0 = p_1 + p_2 + p_3$$



equilibrium structure
no net dipole

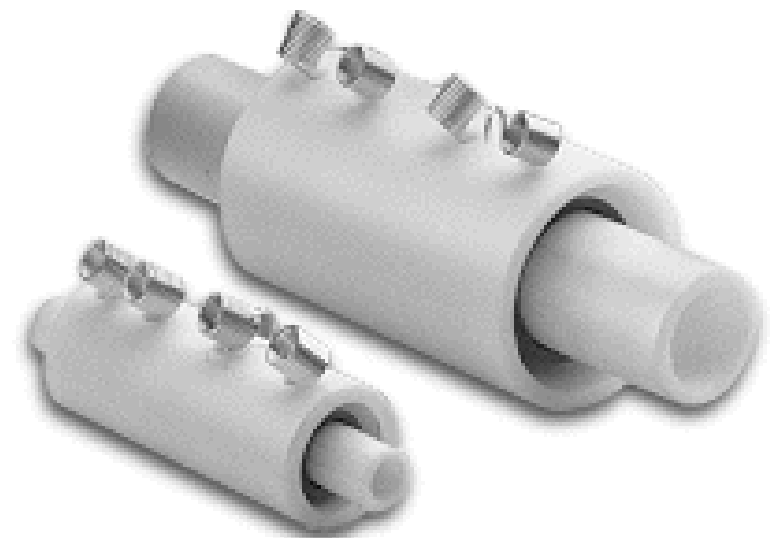
$$p = p_1 + p_2 + p_3$$



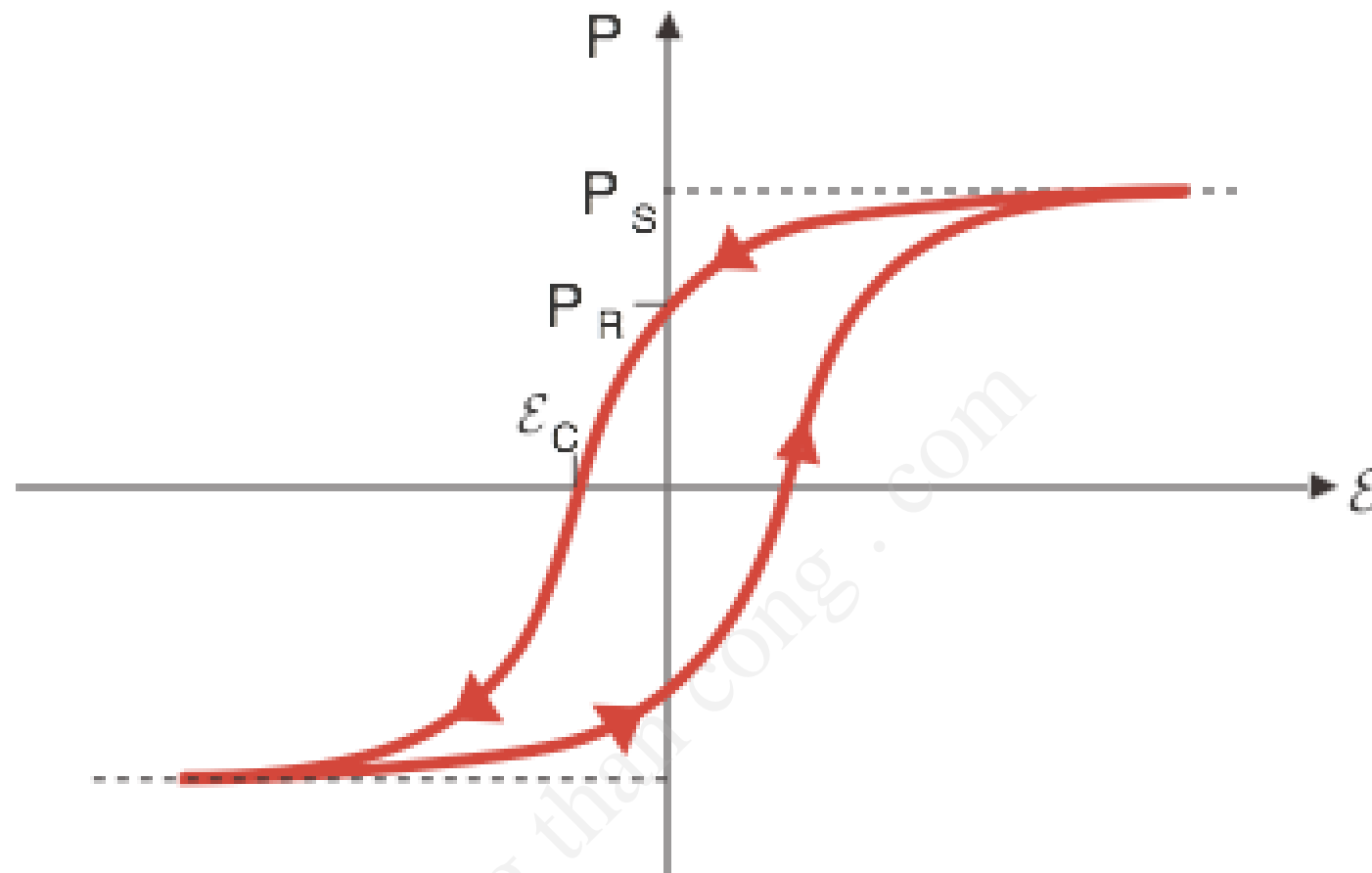
applying stress leads
finite net dipole

Applications (too many to name all....)

- Quartz oscillators in clocks (1 s deviation per year) and micro-balances (detection in ng range)
- microphones, speakers
- positioning: mm range (by inchworms) down to 0.01 nm range

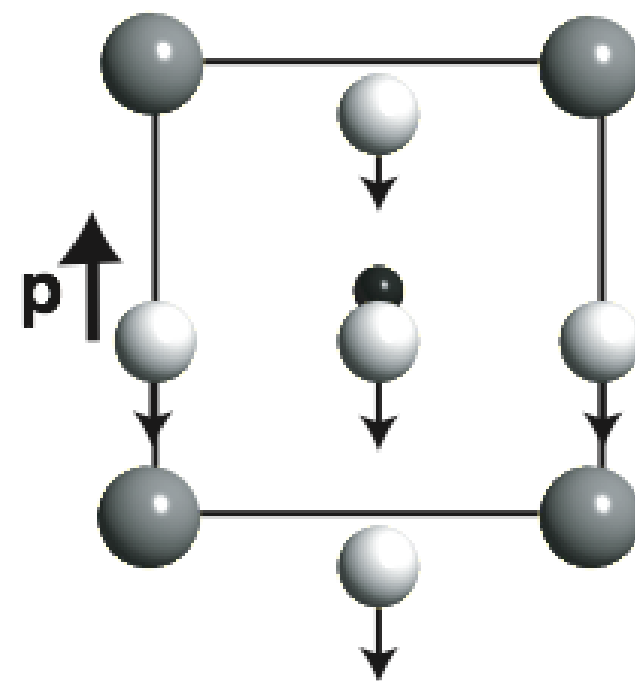
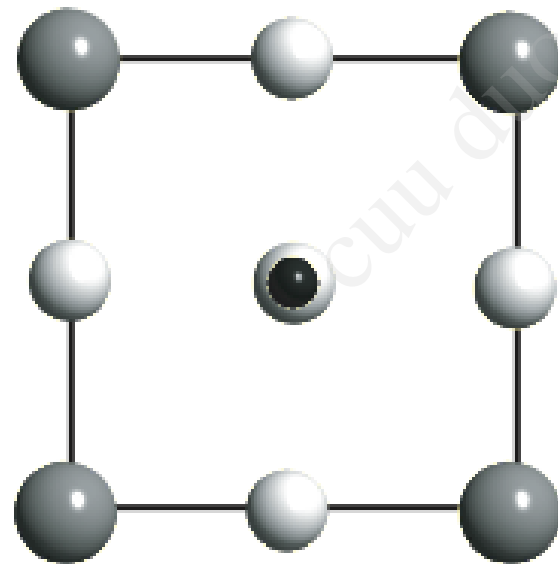
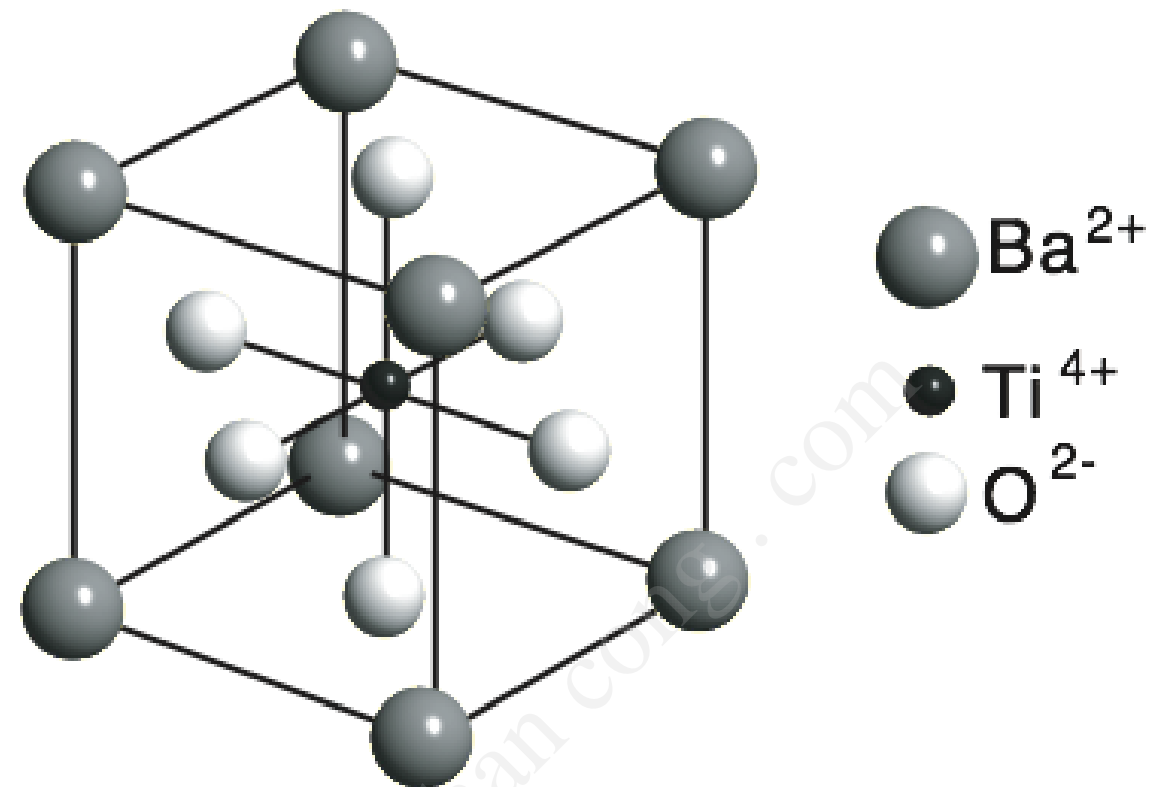


Ferroelectrics



- Spontaneous polarization without external field or stress
- Very similar to ferromagnetism in many aspects: alignment of dipoles, domains, ferroelectric Curie temperature, “paraelectric” above the Curie temperature....
- But: here direct electric field interactions. Direct magnetic field interactions were far too weak to produce ferromagnetism.

Example: barium titanate



ferroelectric

Frequency dependence of the dielectric constant: driven and damped harmonic motion

we start with the usual differential equation

$$\frac{d^2x}{dt^2} + \eta \frac{dx}{dt} + \omega_0^2 x = \frac{e\mathcal{E}_{loc}(x)}{M}$$



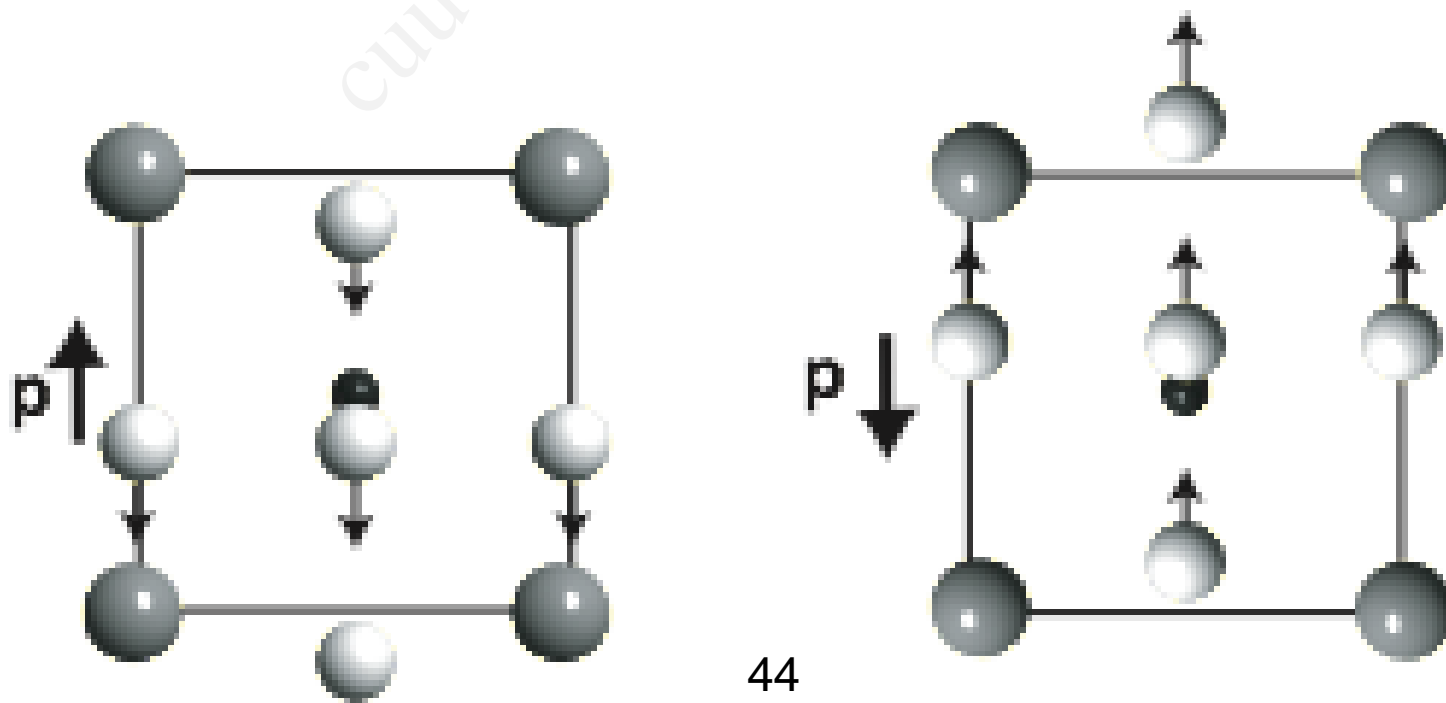
friction
term

harmonic
restoring
term

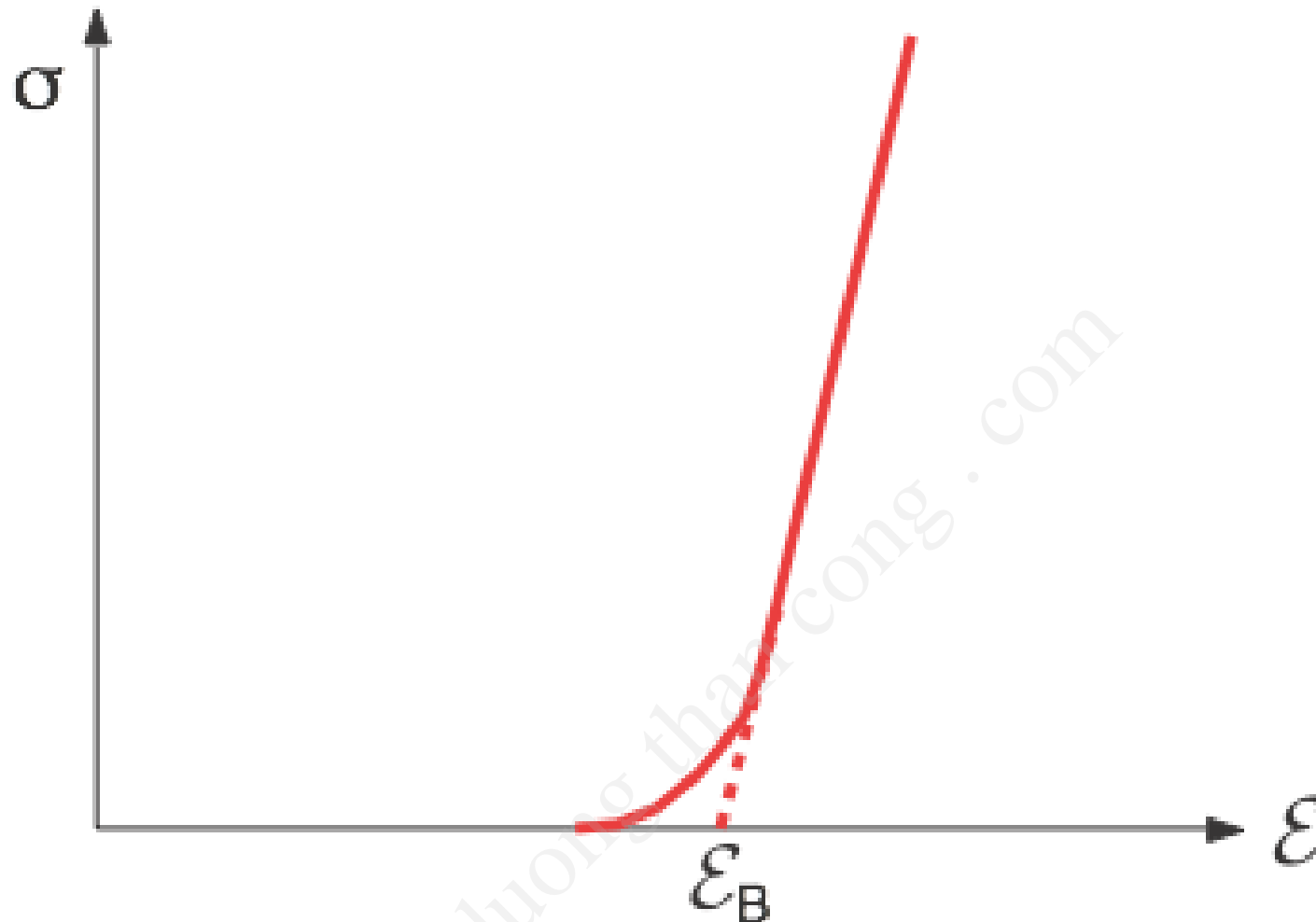
LOCAL
field

Applications of ferroelectric materials

- Most ferroelectrics are also piezoelectric (but not the other way round) and can be applied accordingly.
- Ferroelectrics have a high dielectric constant and can be used to build small capacitors.
- Ferroelectrics can be switched and used as non-volatile memory (fast, low-power, many cycles).



Dielectric breakdown



- For a very high electric field, the dielectric becomes conductive.
- Mostly by kinetic energy: if some free electrons gather enough kinetic energy to free other electrons, an avalanche effect sets in (intrinsic breakdown)